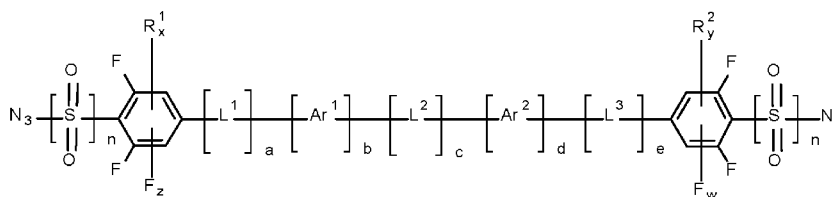




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(54) Title: AZIDE-BASED CROSSLINKING AGENTS



(1)

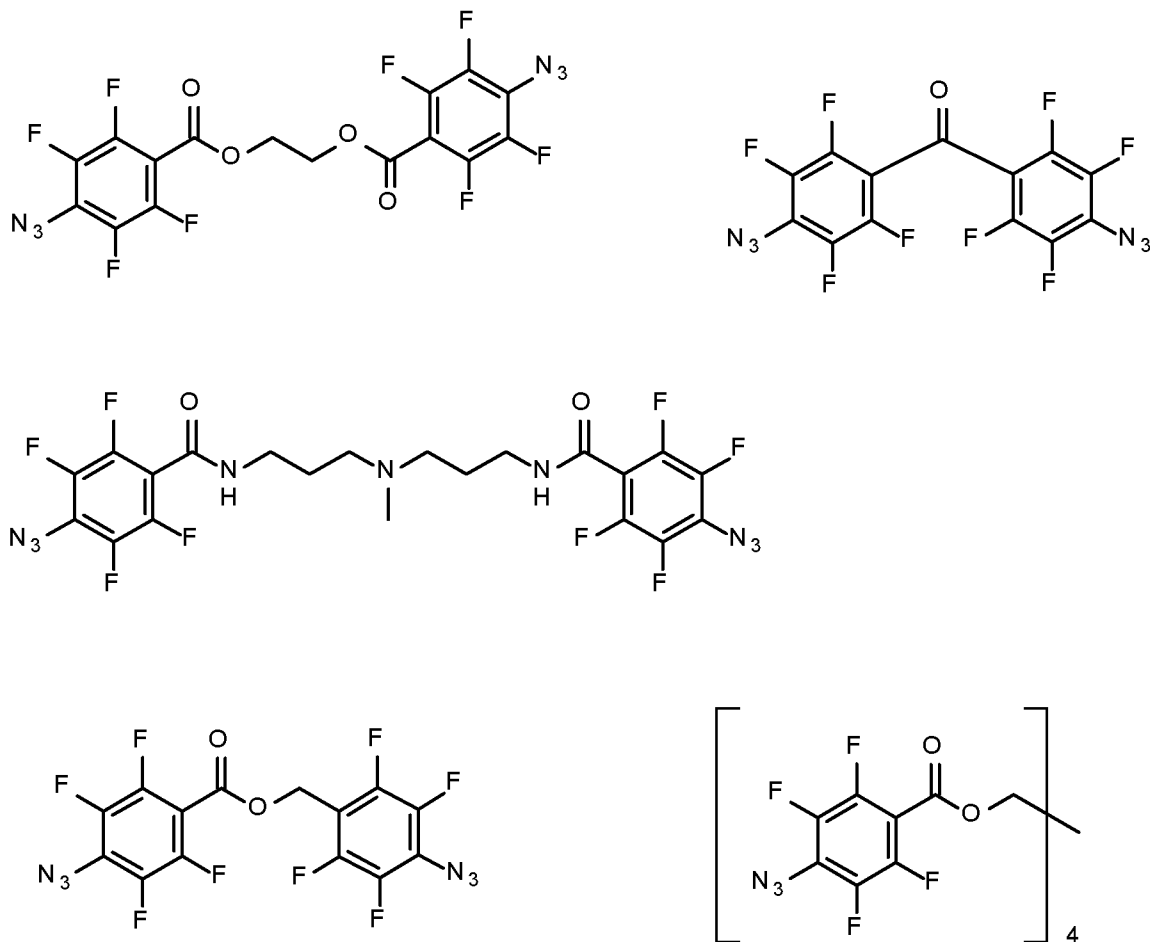
(57) **Abstract:** The present invention provides compounds of formula (1) a process for their preparation, a solution comprising these compounds, a process for the preparation of a device using the solution, devices obtainable by the process and the use of the bis-azide-type compounds as cross-linkers.

Azide-Based Crosslinking Agents

Description

- 5 The present invention relates bis-azide-type compounds, to a process for their preparation, to a solution comprising these compounds, to a process for the preparation of a device using this solution, to devices obtainable by this process and to the use of the bis-azide-type compounds as cross-linkers.
- 10 The preparation of electronic devices such as field effect transistor (FET) devices, light emitting devices (LED) and photovoltaic (PV) devices usually comprises the application and structuring, also called patterning, of various layers such as the application and structuring of the electrodes, as well as, the application and structuring of the semiconducting layer, the dielectric layer and of other layers such as barrier layers.
- 15 The electrode material is usually applied by evaporation followed by structuring of the electrode material layer using photolithography, which involves the application of a photoresist-layer, exposure of the photoresist-layer to radiation using a mask, removal of the photo-resist not-exposed to radiation, etching of the exposed electrode material, and removal of the remaining
- 20 photo-resist.
- The most convenient way to apply the semiconducting layer, the dielectric layer and other layers such as barrier layers is by solution processing techniques such as spin coating or printing. When using liquid processing techniques it is important that the solution of the layer to be applied does not dissolve the layer already present in the device. Thus, one needs to either use
- 25 solvents that do not dissolve the layer already present, so-called orthogonal solvents, or render the layer already present in the device insoluble or less soluble towards the solvent of the next layer to be applied. One way to render a polymer layer insoluble or less soluble towards the solvent of the next layer to be applied is by cross-linking this polymer layer. Depending on the
- 30 cross-linkers used, the crosslinking can be initiated by thermal treatment or by radiation treatment. Radiation treatment has the advantage compared to thermal treatment that by using a mask only part of the polymer layer are cross-linked so that the cross-linking and the structuring step can be combined in one step. The not cross-linked polymer can be easily removed by washing with a suitable solvent, whereas structuring of a polymer layer cross-linked by thermal
- 35 treatment is usually performed using photolithography, which involves a series of steps as outlined above for the application and structuring of the electrodes.
- Bis-azide-type compounds are cross-linkers that can be activated by radiation treatment. Several bis-azide-type compounds and their application in the preparation of electronic devices
- 40 have already been described.

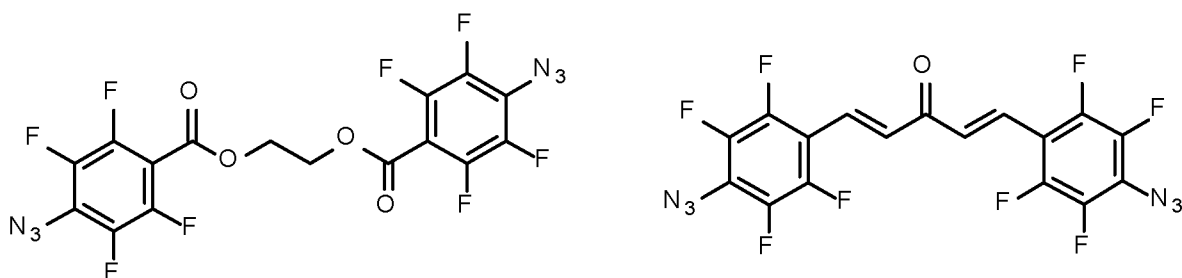
Cai, S.X.; Glenn, D.J.; Kanskar, M.; Wybourne, M.N.; Keana, J.F.W. *Chem. Mater.* **1994**, *6*, 1822-1829 describes the following bis-azide-type compounds

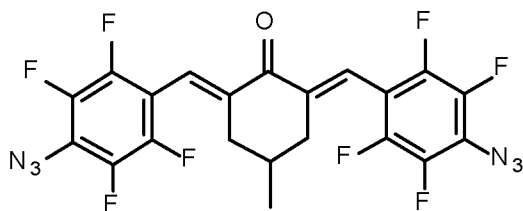


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Polystyrene mixtures containing the cross-linkers above were evaluated as deep-UV and electron beam resists.

- 10 Yan, M.; Cai, S.X.; Wybourne, M.N.; Keana, J.F.W. *J. Mater. Chem.* **1996**, *6*, 1249-1252 describes the following bis-azide-type compounds



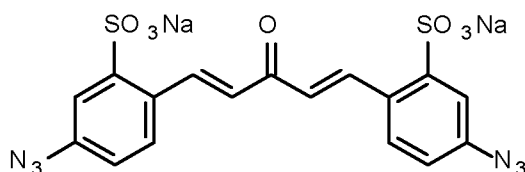


Polyimide mixtures containing the cross-linkers above were evaluated as negative resists.

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Touwslager, F.J.; Willard, N.P.; Leeuw, D.M. *Applied Physics Letters* **2002**, *81*, 4556 describes a lithography process for forming a layer from poly(3,4-ethylenedioxythiophene) (PEDOT). The fully water-borne process is based on photocross-linking PEDOT using the following bis-azide-type compound

10

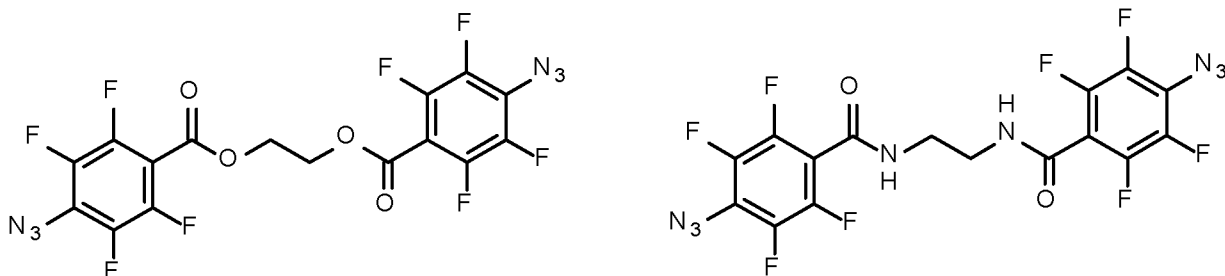


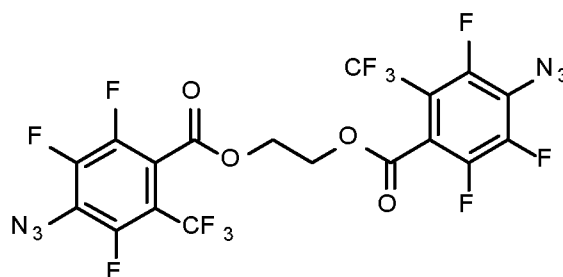
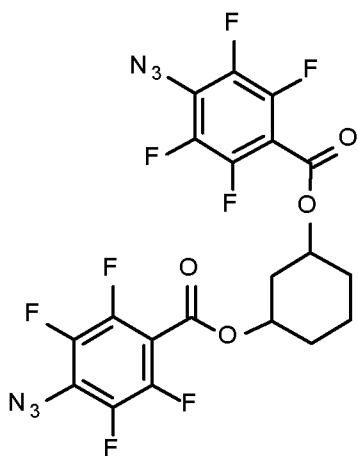
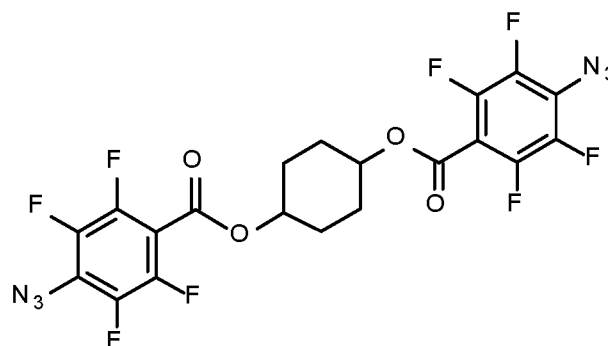
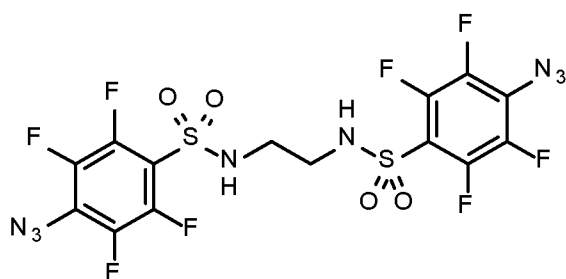
The technology has been applied to fabricate an all-polymer field-effect transistor and integrated circuit.

15

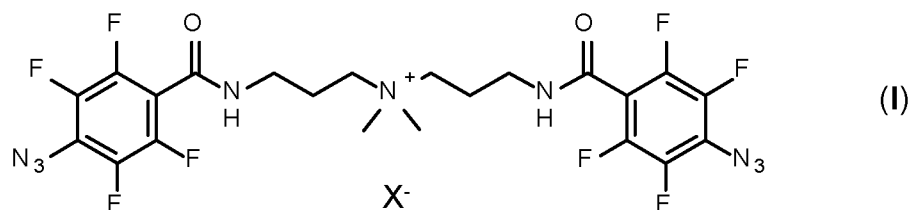
WO 04/100282 describes a method of forming a polymer device including the steps of (i) depositing on a substrate a solution comprising a polymer or oligomer and a crosslinking moiety to form a layer, (ii) curing the layer formed in step (i) under conditions to form an insoluble cross-linked polymer, characterized in that the crosslinking moiety is present in step (i) in an amount in the range of 0.05 to 5 mol% based on the total number of moles of repeat units of the polymer or oligomer and the crosslinking moiety in the solution. Polymer devices include field-effect transistors. It is preferred that the crosslinking moiety has an absorption in the narrow transmission window in the deep ultraviolet. Typically, this will be in the range 200 to 300 nm. WO 04/100282 exemplifies the following cross-linking moieties:

25



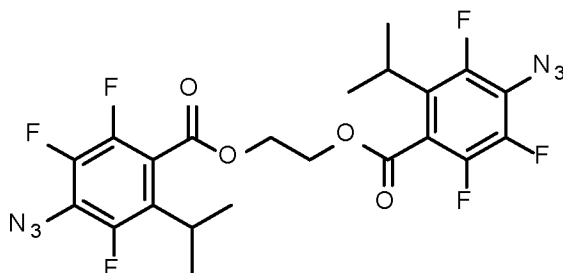


WO 2007/004995 describes a class of cross-linking compound, said compound comprising (i) one or more fluorinated aromatic group and (ii) one or more ionisable group, wherein the cross-linking compound is soluble in at least one polar solvent. The general formula of this class of cross-linking compound is given by formula $N_3-Ar_FZ(R)-N_3$ (I), wherein Ar_FZ comprises one or more fluorinated aromatic groups, and R comprises one or more ionisable group, wherein the cross-linking compound is soluble in at least one polar solvent. WO 2007/004995 also describes a process of forming a device comprising a polymer is provided, the process includes the steps of (i) depositing a film from a solution comprising a polymer and the crosslinking compound on a substrate and (ii) soft-baking the film at a temperature between 100 to 130 °C; and (iii) exposing the solution in step (ii) to radiation having a wavelength in a range of 250 to 450 nm. Exemplified is the cross-linking compound of formula



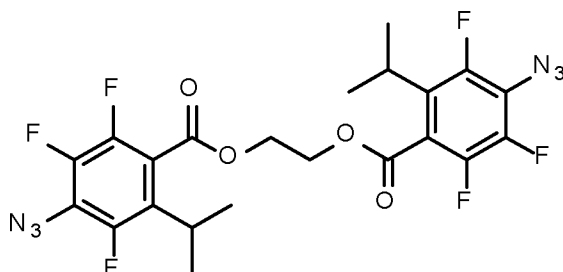
wherein X is selected from I, PF_6 , BF_4 , ClO_4 and CF_3COO .

WO 2009/068884 describes a supported polymer heterostructure and methods of manufacture. The heterostructure is suitable for use in a range of applications which require semiconductor devices including photovoltaic devices and light-emitting diode devices. For example, a process is described which comprises the steps of preparing a solution of poly(9,9'-dioctylfluorene-co-bis-N,N'-(4-butylphenyl)-bis-N,N-phenyl-1,4-phenylene diamine), polystyrene and the following bis-azide-type photocross-linker



in toluene, spincoating this solution on a support, removing polystyrene by methyl ethyl ketone treatment, and exposing the remaining sample to UV light (254 nm).

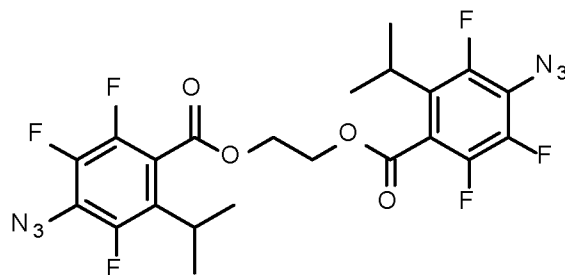
Png, R.-Q.; Chia, P.-J.; Tang, J.-C.; Liu, B.; Sivaramakrishnan S.; Zhou, M.; Khong, S.-H.; Chan, H.S.O.; Burroughes, J.H.; Chua, L.-L.; Friend, R.H.; Ho, P.K.H. *Nature Materials* 2010, 9(2), 152-152 describes that sterically hindered bis(fluorophenyl azides) can be mixed generally into polymer organic semiconductors to cause photocross-linking when exposed to deep-ultraviolet light (254 nm wavelength). An example of a sterically hindered bi(fluorophenyl azide) is



For example, a preparation of an OFET is described which comprises the step of photocross-linking poly 2,5-bis(3-tetradecylthiophene-2-yl)thieno[3,2-b]thiophene) films on an octadecyltrichlorosilylated thermal oxide gate dielectric with p⁺⁺-Si back gate and lithographically patterned AU source-drain electrodes.

WO 2011/068482 describes the cross-linking moiety having a general formula N₃-Ar_F-W (I), wherein Ar_F comprises a fluorinated phenyl azide group having at least one non-fluorine substituent that is bulkier than fluorine at a meta position relative to the azide group, and W comprises

an electron withdrawing group. WO 2011/068482 also describes a solution comprising the cross-linking moiety, and optionally a polymer or oligomer. WO 2011/068482 also describes a method for forming a polymer device comprising the steps of (a) depositing a solution comprising a polymer or oligomer and a cross-linking moiety on a substrate to form a layer, and (b) curing the layer to form an insoluble cross-linked polymer. The device may be a polymer FET device. For example, example 3 of WO 2011/068482 describes the following cross-linking moiety



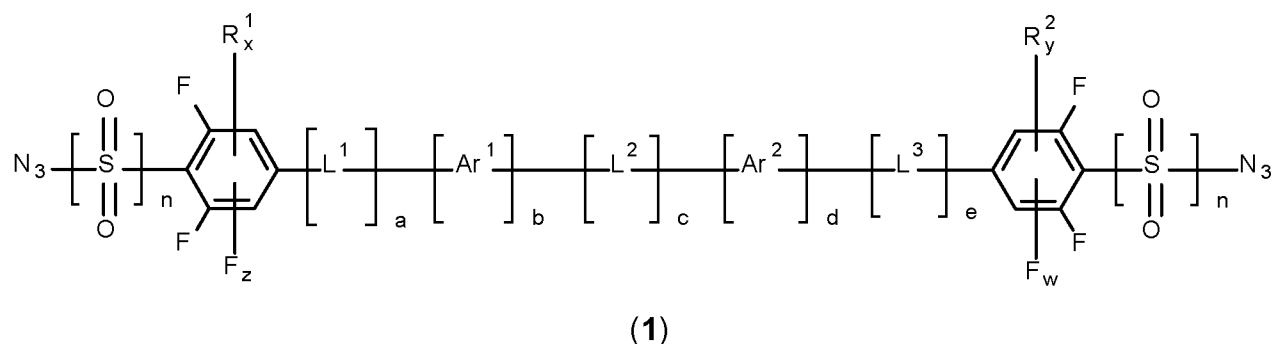
The bis-azide-type compounds described in the literature citations above usually absorb at a wavelength of 254 nm.

However, in the preparation of electronic devices, the photoresist-layer used when structuring the electrode material layer or other layers is usually exposed to a wavelength in the range of 300 to 450 nm, in particular to wavelengths of 365 nm, 405 nm or 436 nm, which correspond to the so-called i-line (365 nm), h-line (405 nm) and g-line (436 nm) of a Hg lamp. Thus, it would be very convenient to have bis-azide-type compounds that also absorb at a wavelength in the range of 300 to 450 nm, preferably have their absorption maximum at or close by a wavelength of 365 nm, 405 nm or 436 nm. This would allow the preparation of devices using the same wavelength for the photoresist-layer and for the crosslinking of the polymer layer, without the need to adjust the wavelength of the photo-device or to even replace the photo-device by a radiation device suitable for cross-linking of the polymer layer during the preparation process.

Thus, it was the object of the present invention to provide bis-azide-type compounds that absorb at a wavelength in the range of 300 to 450 nm, and ideally, but not necessarily, have their absorption maximum near or close by a wavelength usually used in photolithography such as 365 nm, 405 nm or 436 nm.

This object is solved by the compounds of claim 1, the process of claim 8, the solution of claim 9, the process of claim 12, and by the device of claim 15.

The compounds of the present invention are of formula



5

wherein

a is 0, 1 or 2,

b is 1, 2, 3 or 4,

c is 0 or 1,

10

d is 0, 1, 2, 3 or 4,

e is 0, 1 or 2,

x is 0, 1 or 2,

y is 0, 1 or 2,

15

z is 0, 1 or 2,

w is 0, 1 or 2,

n is 0 or 1,

20 Ar¹ and Ar² are independently from each other and at each occurrence an aromatic or heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H,

25 C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^{aa} at each occurrence selected from the group consisting of phenyl, COOR¹², CONR¹²R¹³, COR¹², SO₃R¹², CN, NO₂, halogen, OR¹², SR¹², NR¹¹R¹², OCOR¹² and NR¹²COR¹³,

30 wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{ab} at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR¹², CONR¹²R¹³, COR¹², SO₃R¹², CN, NO₂, halogen, OR¹², SR¹², NR¹²R¹³, OCOR¹² and NR¹²COR¹³,

wherein R¹² and R¹³ are independently from each other and at each occurrence

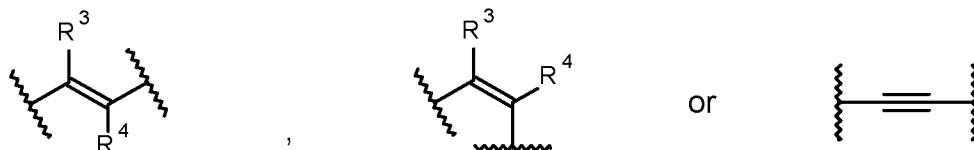
C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl, and

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wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B,

5

L¹ and L³ are independently from each other and at each occurrence



10

wherein

R³ and R⁴ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR²⁰, CONR²⁰R²¹, COR²⁰, SO₃R²⁰, CN, NO₂, or halogen,

15

wherein R²⁰ and R²¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^b at each occurrence selected from the group consisting of phenyl, COOR²², CONR²²R²³, COR²², SO₃R²², CN, NO₂, halogen, OR²², SR²², NR²²R²³, OCOR²² and NR²²COR²³,

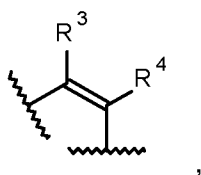
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wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^c at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR²², CONR²²R²³, COR²², SO₃R²², CN, NO₂, halogen, OR²², SR²², NR²²R²³, OCOR²² and NR²²COR²³,

25

wherein R²² and R²³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl,

or, if L¹ or L³ are



30

R³ and R⁴ together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A,

35

L² is a linking moiety A,

and

R^1 and R^2 are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl, 5 to 12 membered heteroaryl, $COOR^{30}$, $CONR^{30}R^{31}$, COR^{30} , SO_3R^{30} , CN, NO_2 , halogen, OR^{30} , SR^{30} , $NR^{30}R^{31}$, $OCOR^{30}$ or $NR^{30}COR^{31}$,

wherein R^{30} and R^{31} are independently from each other and at each occurrence H,

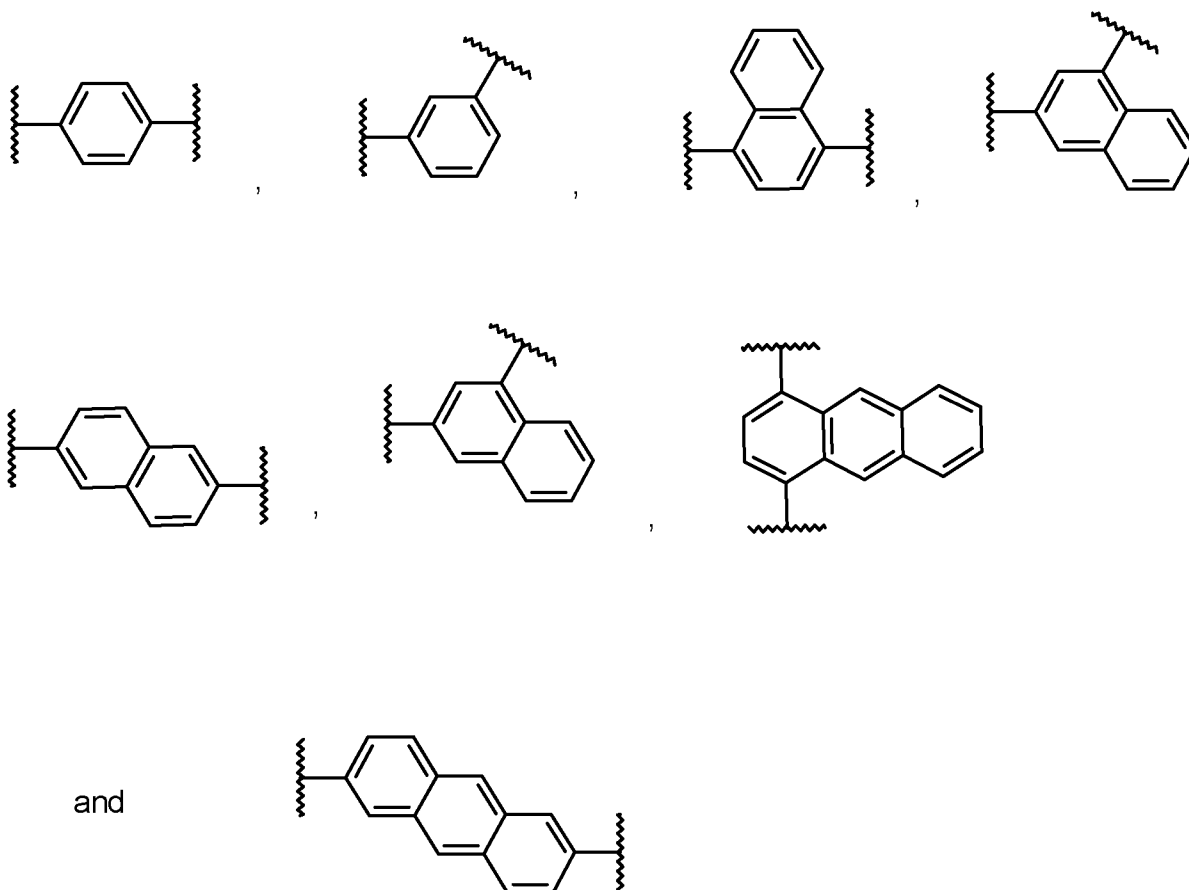
C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl or 5 to 12 membered heteroaryl,

wherein C_{1-20} -alkyl and C_{5-8} -cycloalkyl can be substituted with one or more substituents R^d at each occurrence selected from the group consisting of phenyl, $COOR^{32}$, $CONR^{32}R^{33}$, COR^{32} , SO_3R^{32} , CN, NO_2 , halogen, OR^{32} , SR^{32} , $NR^{32}R^{33}$, $OCOR^{32}$ and $NR^{32}COR^{33}$,

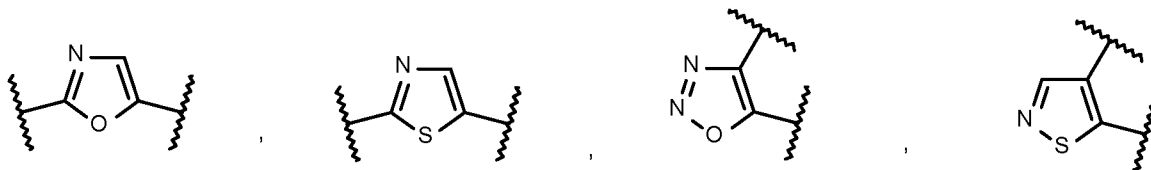
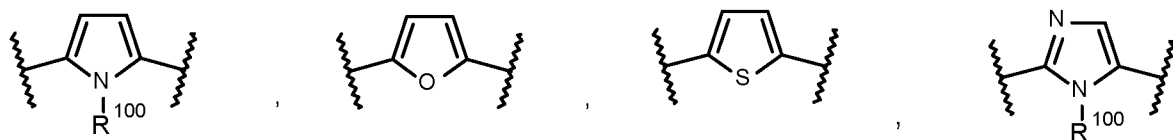
wherein C_{6-14} -aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^e at each occurrence selected from the group consisting of C_{1-10} -alkyl, cyclopentyl, cyclohexyl, $COOR^{32}$, $CONR^{32}R^{33}$, COR^{32} , SO_3R^{32} , CN, NO_2 , halogen, OR^{32} , SR^{32} , $NR^{32}R^{33}$, $OCOR^{32}$ and $NR^{32}COR^{33}$,

wherein R^{32} and R^{33} are independently from each other and at each occurrence C_{1-10} -alkyl, cyclopentyl, cyclohexyl or phenyl.

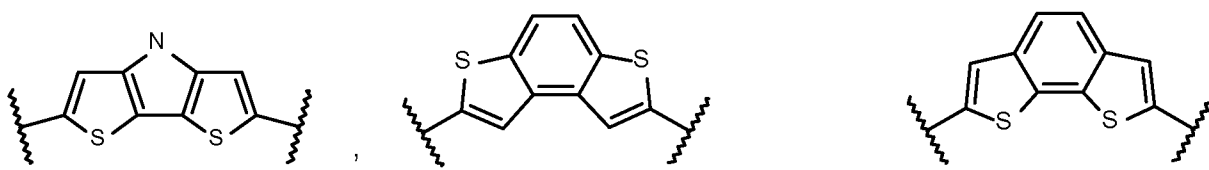
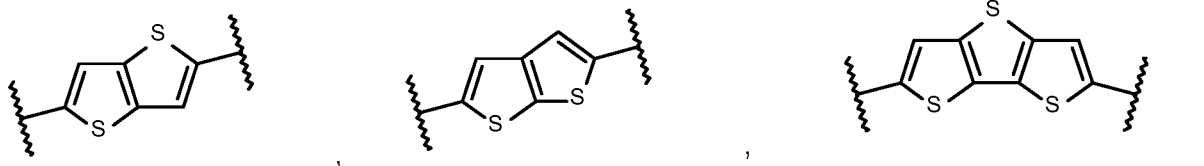
Examples of aromatic moieties are C_{6-14} -aromatic moieties such as



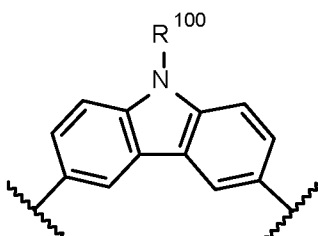
Examples of heteroaromatic moieties are 5 to 14 membered heteroaromatic moieties such as



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and



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wherein R^{100} is C_{1-10} -alkyl.

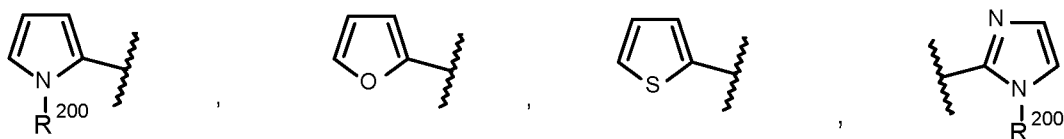
15 C_{1-10} -alkyl and C_{1-20} -alkyl can be branched or unbranched. Examples of C_{1-10} -alkyl are methyl, ethyl, butyl, iso-butyl, sec-butyl, tert-butyl, pentyl, isopentyl, hexyl, heptyl, octyl, 1,1-dimethyl-3,3-dimethylbutyl, nonyl and decyl. Examples of C_{1-20} -alkyl are C_{1-10} -alkyl, undecyl, dodecyl, tridecyl, tetradecyl, pentadecyl, hexadecyl, heptadecyl, octadecyl, nonadecyl and eicosyl. Examples of C_{3-6} -alkyl are isopropyl, tert-butyl, and isopentyl.

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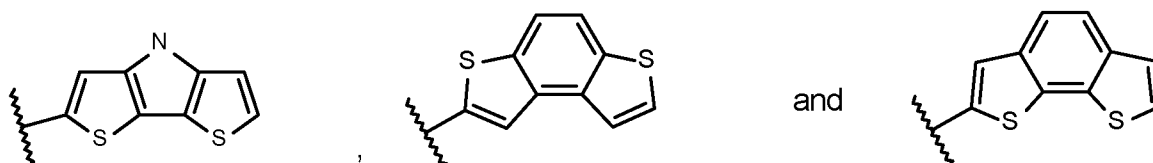
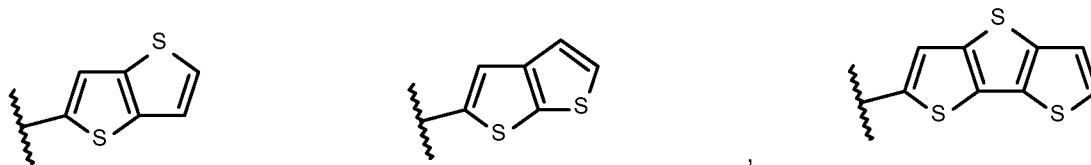
Examples of C₅₋₈-cycloalkyl are cyclopentyl, cyclohexyl, cycloheptyl and cyclooctyl.

5 Examples of C₆₋₁₄-aryl are phenyl and naphthyl.

Examples of 5 to 12 membered heteroaryl are



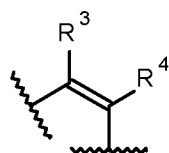
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Examples of halogen are F, Cl, Br and I.

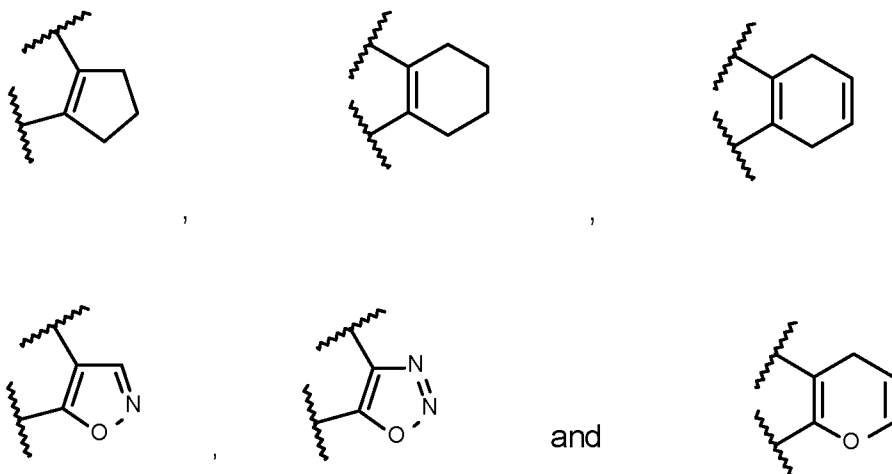
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Examples of L¹ and L³, wherein L¹ and L³ are



20

and R³ and R⁴ together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A, are



- 5 Examples of linking moiety A are C₁₋₁₀-alkylene, C₂₋₁₀-alkenylene, C₅₋₈-cycloalkylene, C₁₋₄-alkylene-C₅₋₈-cycloalkylene-C₁₋₄-alkylene, C₁₋₄-alkylene-phenylene-C₁₋₄-alkylene, C₂₋₄-alkenylene-C₅₋₈-cycloalkylene-C₂₋₄-alkenylene and C₂₋₄-alkenylene-phenylene-C₂₋₄-alkenylene, which can be substituted with one or more substituent R^f at each occurrence selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR⁴⁰, CONR⁴⁰R⁴¹, COR⁴⁰, SO₃R⁴⁰, CN, NO₂, halogen, OR⁴⁰, SR⁴⁰, NR⁴⁰R⁴¹, OCOR⁴⁰ and NR⁴⁰COR⁴¹,
- 10 wherein R⁴⁰ and R⁴¹ are independently from each other and at each occurrence H, C₁₋₁₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^{fa} at each occurrence selected from the group consisting of phenyl, COOR⁴², CONR⁴²R⁴³, COR⁴², SO₃R⁴², CN, NO₂, halogen, OR⁴², SR⁴², NR⁴²R⁴³, OCOR⁴² and NR⁴²COR⁴³,
- 15 wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{fb} at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR⁴², CONR⁴²R⁴³, COR⁴², SO₃R⁴², CN, NO₂, halogen, OR⁴², SR⁴², NR⁴²R⁴³, OCOR⁴² and NR⁴²COR⁴³,
- 20 wherein R⁴² and R⁴³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl, and
- 25 wherein one or more CH₂ groups of C₁₋₁₀-alkylene, C₁₋₄-alkylene, C₂₋₁₀-alkenylene, C₂₋₄-alkenylene and/or C₅₋₈-cycloalkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,
- wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl.
- 30

Examples of linking moiety B is C₁₋₄-alkylene, which can be substituted with one or more C₁₋₁₀-alkyl, wherein one or more CH₂ groups of C₁₋₄-alkylene can be replaced by C=O, (C=O)O, (C=O)NR⁶⁰, SO₂-NR⁶⁰, NR⁶⁰, NR⁶⁰R⁶¹, O or S,

wherein R⁶⁰ and R⁶¹ are independently from each other and at each occurrence

5 C₁₋₁₀-alkyl.

Examples of C₁₋₄-alkylene are methylene, ethylene, propylene and butylene. Examples of C₁₋₁₀-alkylene are C₁₋₄-alkylene as well as pentylene, hexylene, heptylene, octylene, nonylene and decylene.

Examples of C₂₋₄-alkenylene are methenylene, ethenylene, propenylene and butenylene. Examples of C₂₋₁₀-alkenylene are C₂₋₄-alkenylene as well as pentenylene, hexenylene, heptenylene, octenylene, nonenylene and decenylene.

15 Examples of C₅₋₈-cycloalkylene are cyclopentylene, cyclohexylene, cycloheptylene and cyclooctylene.

20 Preferably,
a and e are the same and are 0 or 1,
b is 1, 2 or 3,
c is 0 or 1, and
d is 0, 1, 2 or 3.

25 More preferably,
a and e are the same and are 0 or 1,
b is 1,
c is 0 or 1, and
30 d is 0 or 1.

Preferably,
x and y are the same and are 0, 1 or 2, and
35 z and w are the same and are 0, 1 or 2.

More preferably,
x and y are the same and are 0 or 1, and
z and w are the same and are 1 or 2.

40 Most preferably,
x and y are the same and are 0,
z and w are the same and are 2.

Preferably, n is 0.

Preferably, Ar¹ and Ar² are independently from each other and at each occurrence an aromatic or heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H,

C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, and

wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B.

More preferably, Ar¹ and Ar² are independently from each other and at each occurrence a C₆₋₁₄-aromatic or a 5 to 12 membered heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H,

C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

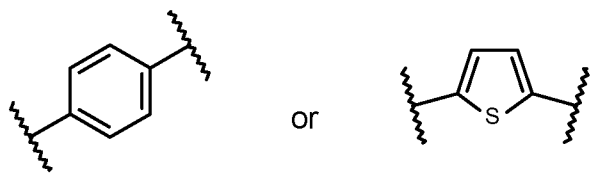
wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B.

Even more preferably, Ar¹ and Ar² are the same and are a C₆₋₁₄-aromatic or a 5 to 12 membered heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl and OR¹⁰,

wherein R¹⁰ is independently from each other and at each occurrence C₁₋₂₀-alkyl, and

wherein Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B, wherein the linking moiety B is C₁₋₄-alkylene, which can be substituted with one or more C₁₋₁₀-alkyl.

Most preferably, Ar¹ and Ar² are the same and are



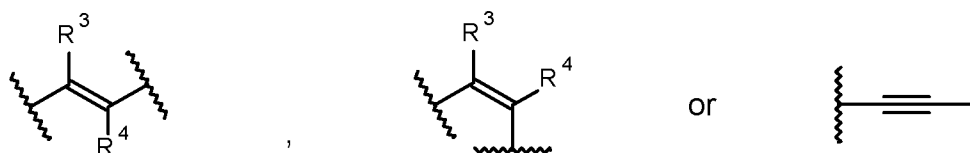
which can be substituted with one or more substituent R^a selected from the group consisting of C_{1-10} -alkyl and OR^{10} ,

5 wherein R^{10} is independently from each other and at each occurrence C_{1-10} -alkyl, and

wherein Ar^1 and Ar^2 , both connected to L^2 or if $c = 0$ to each other, can be additionally linked by one or more L^a , wherein L^a is a linking moiety B, wherein the linking moiety B is methylene substituted with one or more C_{1-10} -alkyl.

10

Preferably, L^1 and L^3 are independently from each other and at each occurrence



15

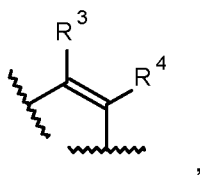
wherein

R^3 and R^4 are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl, 5 to 12 membered heteroaryl, $COOR^{20}$, $CONR^{20}R^{21}$, COR^{20} , SO_3R^{20} , CN, NO_2 , or halogen,

20 wherein R^{20} and R^{21} are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl or 5 to 12 membered heteroaryl,

or, if L^1 or L^3 are

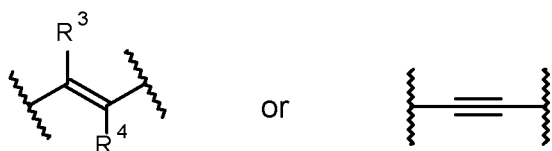
25



R^3 and R^4 together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A.

30

More preferably, L^1 and L^3 are the same and are



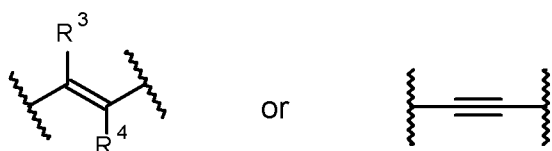
wherein

5 R^3 and R^4 are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl, 5 to 12 membered heteroaryl, $COOR^{20}$, $CONR^{20}R^{21}$, COR^{20} , SO_3R^{20} , CN, NO_2 or halogen,

wherein R^{20} and R^{21} are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl or 5 to 12 membered heteroaryl.

10

Even more preferably, L^1 and L^3 are the same and are



15

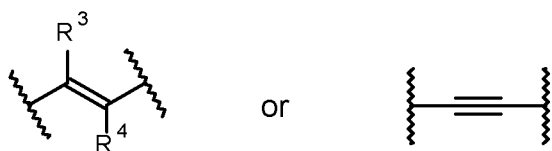
wherein

R^3 and R^4 are independently from each other and at each occurrence H, C_{1-20} -alkyl, $COOR^{20}$, $CONR^{20}R^{21}$, COR^{20} , SO_3R^{20} , CN, NO_2 or halogen,

wherein R^{20} and R^{21} are independently from each other and at each occurrence H or C_{1-20} -alkyl.

20

Most preferably, L^1 and L^3 are the same and are



25

wherein

R^3 and R^4 are H.

30 Preferably, L^2 is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C_{1-10} -alkylene, C_{2-10} -alkenylene, C_{5-8} -cycloalkylene, C_{1-4} -alkylene- C_{5-8} -cycloalkylene- C_{1-4} -alkylene, C_{1-4} -alkylene-phenylene- C_{1-4} -alkylene, C_{2-4} -alkenylene- C_{5-8} -cycloalkylene- C_{2-4} -alkenylene and C_{2-4} -alkenylene-phenylene- C_{2-4} -alkenylene, which can be substituted with one or more substituent R^f at each occurrence selected from the group consisting of C_{1-20} -alkyl,

C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR⁴⁰, CONR⁴⁰R⁴¹, COR⁴⁰, SO₃R⁴⁰, CN, NO₂, halogen, OR⁴⁰, SR⁴⁰, NR⁴⁰R⁴¹, OCOR⁴⁰ and NR⁴⁰COR⁴¹,

wherein R⁴⁰ and R⁴¹ are independently from each other and at each occurrence H, C₁₋₁₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^{fa} at each occurrence selected from the group consisting of phenyl, COOR⁴², CONR⁴²R⁴³, COR⁴², SO₃R⁴², CN, NO₂, halogen, OR⁴², SR⁴², NR⁴²R⁴³, OCOR⁴² and NR⁴²COR⁴³,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{fb} at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR⁴², CONR⁴²R⁴³, COR⁴², SO₃R⁴², CN, NO₂, halogen, OR⁴², SR⁴², NR⁴²R⁴³, OCOR⁴² and NR⁴²COR⁴³,

wherein R⁴² and R⁴³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl, and

wherein one or more CH₂ groups of C₁₋₁₀-alkylene, C₁₋₄-alkylene, C₂₋₁₀-alkenylene, C₂₋₄-alkenylene and/or C₅₋₈-cycloalkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence

C₁₋₁₀-alkyl.

More preferably, L² is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C₁₋₁₀-alkylene, C₂₋₁₀-alkenylene, C₅₋₈-cycloalkylene, C₁₋₄-alkylene-C₅₋₈-cycloalkylene-C₁₋₄-alkylene, C₁₋₄-alkylene-phenylene-C₁₋₄-alkylene, C₂₋₄-alkenylene-C₅₋₈-cycloalkylene-C₂₋₄-alkenylene and C₂₋₄-alkenylene-phenylene-C₂₋₄-alkenylene, which can be substituted with one or more substituent R^f at each occurrence selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR⁴⁰, CONR⁴⁰R⁴¹, COR⁴⁰, SO₃R⁴⁰, CN, NO₂, halogen, OR⁴⁰, SR⁴⁰, NR⁴⁰R⁴¹, OCOR⁴⁰ and NR⁴⁰COR⁴¹,

wherein R⁴⁰ and R⁴¹ are independently from each other and at each occurrence H, C₁₋₁₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, and

wherein one or more CH₂ groups of C₁₋₁₀-alkylene, C₁₋₄-alkylene, C₂₋₁₀-alkenylene, C₂₋₄-alkenylene and/or C₅₋₈-cycloalkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence

C₁₋₁₀-alkyl.

Even more preferably, L² is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C₁₋₁₀-alkylene, C₂₋₁₀-alkenylene, C₅₋₈-cycloalkylene, C₁₋₄-alkylene-C₅₋₈-cycloalkylene-C₁₋₄-alkylene, C₁₋₄-alkylene-phenylene-C₁₋₄-alkylene, C₂₋₄-alkenylene-C₅₋₈-cycloalkylene-C₂₋₄-alkenylene and C₂₋₄-alkenylene-phenylene-C₂₋₄-alkenylene,

wherein one or more CH₂ groups of C₁₋₁₀-alkylene, C₁₋₄-alkylene, C₂₋₁₀-alkenylene, C₂₋₄-alkenylene and/or C₅₋₈-cycloalkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

- 5 wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl.

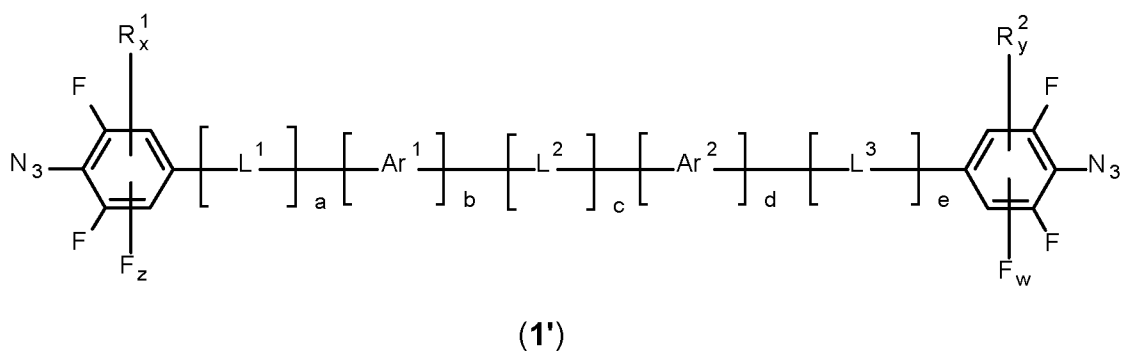
- 10 Most preferably, L² is a linking moiety A, wherein the linking moiety A is C₁₋₁₀-alkylene, wherein one or more CH₂ groups of C₁₋₁₀-alkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S, wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl.

- 15 Preferably, R¹ and R² are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR³⁰, CONR³⁰R³¹, COR³⁰, SO₃R³⁰, CN, NO₂, halogen, OR³⁰, SR³⁰, NR³⁰R³¹, OCOR³⁰ or NR³⁰COR³¹, wherein R³⁰ and R³¹ are independently from each other and at each occurrence H, 20 C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl.

More preferably, R¹ and R² are the same and are H, C₁₋₂₀-alkyl or C₅₋₈-cycloalkyl.

- 25 Most preferably, R¹ and R² are the same and are branched C₃₋₆-alkyl.

In preferred compounds of formula (1) n is 0, and the compounds are of formula



- 30 wherein
 a is 0, 1 or 2,
 b is 1, 2, 3 or 4,
 c is 0 or 1,
 d is 0, 1, 2, 3 or 4,
 e is 0, 1 or 2,

x is 0, 1 or 2,

y is 0, 1 or 2,

z is 0, 1 or 2,

5 w is 0, 1 or 2,

Ar¹ and Ar² are independently from each other and at each occurrence an aromatic or heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰,
10 CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H,

C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

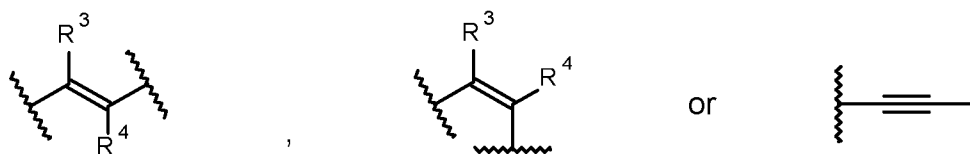
wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^{aa} at each occurrence selected from the group consisting of phenyl, COOR¹², CONR¹²R¹³,
15 COR¹², SO₃R¹², CN, NO₂, halogen, OR¹², SR¹², NR¹¹R¹², OCOR¹² and NR¹²COR¹³,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{ab} at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR¹², CONR¹²R¹³, COR¹², SO₃R¹², CN, NO₂, halogen, OR¹²,
20 SR¹², NR¹²R¹³, OCOR¹² and NR¹²COR¹³,

wherein R¹² and R¹³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl, and

wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B,
25

L¹ and L³ are independently from each other and at each occurrence



wherein

R³ and R⁴ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR²⁰, CONR²⁰R²¹, COR²⁰,
35 SO₃R²⁰, CN, NO₂, or halogen,

wherein R²⁰ and R²¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^b at each occurrence selected from the group consisting of phenyl, COOR²²,

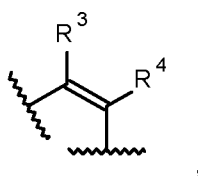
CONR²²R²³, COR²², SO₃R²², CN, NO₂, halogen, OR²², SR²², NR²²R²³, OCOR²² and NR²²COR²³,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^c at each occurrence selected from the group consisting of

C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR²², CONR²²R²³, COR²², SO₃R²², CN, NO₂, halogen, OR²², SR²², NR²²R²³, OCOR²² and NR²²COR²³,

wherein R²² and R²³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl,

or, if L¹ or L³ are



R³ and R⁴ together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A,

L² is a linking moiety A,

and

R¹ and R² are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR³⁰, CONR³⁰R³¹, COR³⁰, SO₃R³⁰, CN, NO₂, halogen, OR³⁰, SR³⁰, NR³⁰R³¹, OCOR³⁰ or NR³⁰COR³¹,

wherein R³⁰ and R³¹ are independently from each other and at each occurrence H,

C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^d at each occurrence selected from the group consisting of phenyl, COOR³², CONR³²R³³, COR³², SO₃R³², CN, NO₂, halogen, OR³², SR³², NR³²R³³, OCOR³² and NR³²COR³³,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^e at each occurrence selected from the group consisting of

C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR³², CONR³²R³³, COR³², SO₃R³², CN, NO₂, halogen, OR³², SR³², NR³²R³³, OCOR³² and NR³²COR³³,

wherein R³² and R³³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl.

In more preferred compounds of formula (1) n is 0, and the compounds are of formula (1'),
wherein

a is 0, 1 or 2,

b is 1, 2, 3 or 4,

c is 0 or 1,

5 d is 0, 1, 2, 3 or 4,

e is 0, 1 or 2,

x is 0, 1 or 2,

y is 0, 1 or 2,

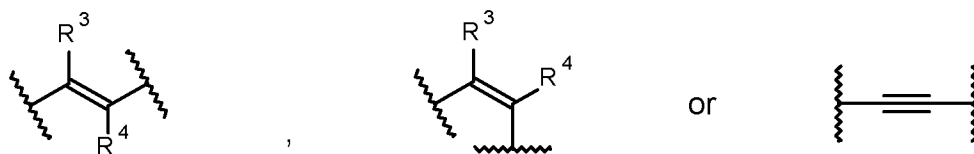
10 z is 0, 1 or 2,

w is 0, 1 or 2,

15 Ar¹ and Ar² are independently from each other and at each occurrence an aromatic or heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹, wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, and

20 wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B,

25 L¹ and L³ are independently from each other and at each occurrence

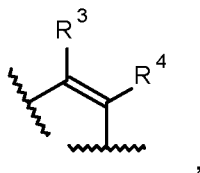


wherein

30 R³ and R⁴ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR²⁰, CONR²⁰R²¹, COR²⁰, SO₃R²⁰, CN, NO₂, or halogen,

wherein R²⁰ and R²¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

35 or, if L¹ or L³ are



R^3 and R^4 together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A,

5

L^2 is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C_{1-10} -alkylene, C_{2-10} -alkenylene, C_{5-8} -cycloalkylene, C_{1-4} -alkylene- C_{5-8} -cycloalkylene- C_{1-4} -alkylene, C_{1-4} -alkylene-phenylene- C_{1-4} -alkylene, C_{2-4} -alkenylene- C_{5-8} -cycloalkylene- C_{2-4} -alkenylene and C_{2-4} -alkenylene-phenylene- C_{2-4} -alkenylene, which can be substituted with one or more substituent R^f at each occurrence selected from the group consisting of C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl, 5 to 12 membered heteroaryl, $COOR^{40}$, $CONR^{40}R^{41}$, COR^{40} , SO_3R^{40} , CN, NO_2 , halogen, OR^{40} , SR^{40} , $NR^{40}R^{41}$, $OCOR^{40}$ and $NR^{40}COR^{41}$,

10

wherein R^{40} and R^{41} are independently from each other and at each occurrence H, C_{1-10} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl or 5 to 12 membered heteroaryl,

15

wherein C_{1-20} -alkyl and C_{5-8} -cycloalkyl can be substituted with one or more substituents R^{fa} at each occurrence selected from the group consisting of phenyl, $COOR^{42}$, $CONR^{42}R^{43}$, COR^{42} , SO_3R^{42} , CN, NO_2 , halogen, OR^{42} , SR^{42} , $NR^{42}R^{43}$, $OCOR^{42}$ and $NR^{42}COR^{43}$,

20

wherein C_{6-14} -aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{fb} at each occurrence selected from the group consisting of C_{1-10} -alkyl, cyclopentyl, cyclohexyl, $COOR^{42}$, $CONR^{42}R^{43}$, COR^{42} , SO_3R^{42} , CN, NO_2 , halogen, OR^{42} , SR^{42} , $NR^{42}R^{43}$, $OCOR^{42}$ and $NR^{42}COR^{43}$,

wherein R^{42} and R^{43} are independently from each other and at each occurrence C_{1-10} -alkyl, cyclopentyl, cyclohexyl or phenyl, and

25

wherein one or more CH_2 groups of C_{1-10} -alkylene, C_{1-4} -alkylene, C_{2-10} -alkenylene, C_{2-4} -alkenylene and/or C_{5-8} -cycloalkylene can be replaced by $C=O$, $(C=O)O$, $(C=O)NR^{50}$, SO_2-NR^{50} , NR^{50} , $NR^{50}R^{51}$, O or S,

wherein R^{50} and R^{51} are independently from each other and at each occurrence

30

C_{1-10} -alkyl,

and

R^1 and R^2 are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl, 5 to 12 membered heteroaryl, $COOR^{30}$, $CONR^{30}R^{31}$, COR^{30} , SO_3R^{30} , CN, NO_2 , halogen, OR^{30} , SR^{30} , $NR^{30}R^{31}$, $OCOR^{30}$ or $NR^{30}COR^{31}$,

35

wherein R^{30} and R^{31} are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl or 5 to 12 membered heteroaryl.

40

In even more preferred compounds of formula (1) n is 0, and the compounds are of formula (1'), wherein

a and e are the same and are 0 or 1,

5 b is 1, 2 or 3,

c is 0 or 1, and

d is 0, 1, 2 or 3,

x and y are the same and are 0, 1 or 2, and

10 z and w are the same and are 0, 1 or 2,

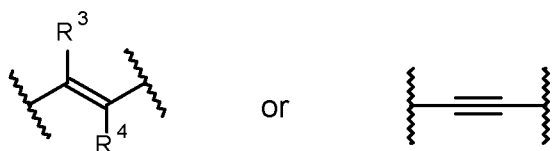
Ar¹ and Ar² are independently from each other and at each occurrence a C₆₋₁₄-aromatic or a 5 to 12 membered heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, and

20 wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B,

L¹ and L³ are the same and are

25



wherein

R³ and R⁴ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR²⁰, CONR²⁰R²¹, COR²⁰, SO₃R²⁰, CN, NO₂, or halogen,

30

wherein R²⁰ and R²¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

35 L² is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C₁₋₁₀-alkylene, C₂₋₁₀-alkenylene, C₅₋₈-cycloalkylene, C₁₋₄-alkylene-C₅₋₈-cycloalkylene-C₁₋₄-alkylene, C₁₋₄-alkylene-phenylene-C₁₋₄-alkylene, C₂₋₄-alkenylene-C₅₋₈-cycloalkylene-C₂₋₄-alkenylene and C₂₋₄-alkenylene-phenylene-C₂₋₄-alkenylene, which can be substituted with one or more substituent R^f at each occurrence selected from the group consisting of C₁₋₂₀-alkyl,

C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR⁴⁰, CONR⁴⁰R⁴¹, COR⁴⁰, SO₃R⁴⁰, CN, NO₂, halogen, OR⁴⁰, SR⁴⁰, NR⁴⁰R⁴¹, OCOR⁴⁰ and NR⁴⁰COR⁴¹,

wherein R⁴⁰ and R⁴¹ are independently from each other and at each occurrence H, C₁₋₁₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, and

5

wherein one or more CH₂ groups of C₁₋₁₀-alkylene, C₁₋₄-alkylene, C₂₋₁₀-alkenylene, C₂₋₄-alkenylene and/or C₅₋₈-cycloalkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence

10

C₁₋₁₀-alkyl,

and

R¹ and R² are the same and are H, C₁₋₂₀-alkyl or C₅₋₈-cycloalkyl.

15

In most preferred compounds of formula (1) n is 0, and the compounds are of formula (1'), wherein

20

a and e are the same and are 0 or 1,

b is 1,

c is 0 or 1, and

d is 0 or 1,

25

x and y are the same and are 0 or 1, and

z and w are the same and are 1 or 2,

Ar¹ and Ar² are the same and are a C₆₋₁₄-aromatic or a 5 to 12 membered heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl and OR¹⁰,

30

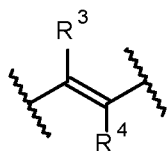
wherein R¹⁰ is independently from each other and at each occurrence C₁₋₂₀-alkyl, and

wherein Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B, wherein the linking moiety B is C₁₋₄-alkylene,

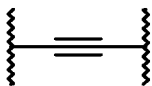
35

which can be substituted with one or more C₁₋₁₀-alkyl,

L¹ and L³ are the same and are



or



40

wherein

R^3 and R^4 are independently from each other and at each occurrence H, C_{1-20} -alkyl, $COOR^{20}$, $CONR^{20}R^{21}$, COR^{20} , SO_3R^{20} , CN, NO_2 or halogen,

wherein R^{20} and R^{21} are independently from each other and at each occurrence H or C_{1-20} -alkyl,

L^2 is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C_{1-10} -alkylene, C_{2-10} -alkenylene, C_{5-8} -cycloalkylene, C_{1-4} -alkylene- C_{5-8} -cycloalkylene- C_{1-4} -alkylene, C_{1-4} -alkylene-phenylene- C_{1-4} -alkylene, C_{2-4} -alkenylene- C_{5-8} -cycloalkylene- C_{2-4} -alkenylene and C_{2-4} -alkenylene-phenylene- C_{2-4} -alkenylene,

wherein one or more CH_2 groups of C_{1-10} -alkylene, C_{1-4} -alkylene, C_{2-10} -alkenylene, C_{2-4} -alkenylene and/or C_{5-8} -cycloalkylene can be replaced by $C=O$, $(C=O)O$, $(C=O)NR^{50}$, SO_2-NR^{50} , NR^{50} , $NR^{50}R^{51}$, O or S,

wherein R^{50} and R^{51} are independently from each other and at each occurrence C_{1-10} -alkyl,

and

R^1 and R^2 are the same and are branched C_{3-6} -alkyl.

In particular preferred compounds of formula (1) n is 0, and the compounds are of formula (1'), wherein

a and e are the same and are 0 or 1,

b is 1,

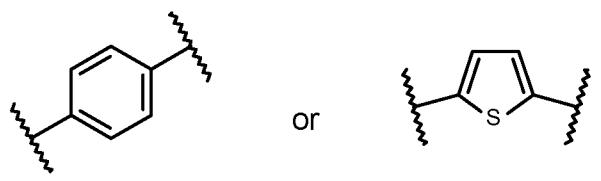
c is 0 or 1, and

d is 0 or 1,

x and y are 0, and

z and w are 2,

Ar^1 and Ar^2 are the same and are



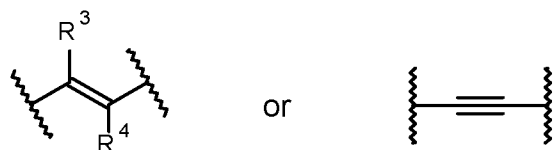
which can be substituted with one or more substituent R^a selected from the group consisting of C_{1-10} -alkyl and OR^{10} ,

wherein R^{10} is independently from each other and at each occurrence C_{1-10} -alkyl, and

wherein Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B, wherein the linking moiety B is methylene substituted with one or more C₁₋₁₀-alkyl,

5

L¹ and L³ are the same and are



10

wherein

R³ and R⁴ are H,

and

15

L² is a linking moiety A, wherein the linking moiety A is C₁₋₁₀-alkylene, wherein one or more CH₂ groups of C₁₋₁₀-alkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S, L² is a linking moiety A, wherein the linking moiety A is C₁₋₁₀-alkylene,

20

wherein one or more CH₂ groups of C₁₋₁₀-alkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl.

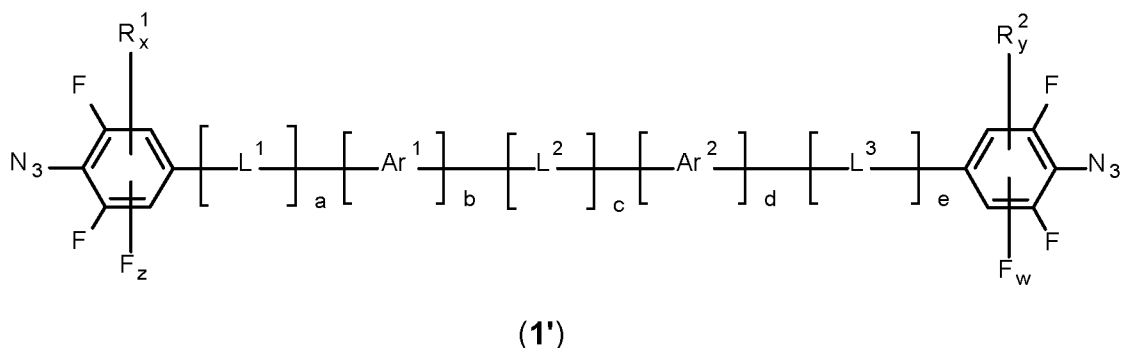
25

wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl.

Also part of the present invention is a process for the preparation of the compounds of formula (1').

30

The process for the preparation of the compounds of formula



wherein

a is 0, 1 or 2,

b is 1, 2, 3 or 4,

c is 0 or 1,

5 d is 0, 1, 2, 3 or 4,

e is 0, 1 or 2,

x is 0, 1 or 2,

y is 0, 1 or 2,

10 z is 0, 1 or 2,

w is 0, 1 or 2,

Ar¹ and Ar² are independently from each other and at each occurrence an aromatic or heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the

15 group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H,

C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^{aa}

20 at each occurrence selected from the group consisting of phenyl, COOR¹², CONR¹²R¹³, COR¹², SO₃R¹², CN, NO₂, halogen, OR¹², SR¹², NR¹¹R¹², OCOR¹² and NR¹²COR¹³,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{ab} at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cy-

25 clopentyl, cyclohexyl, COOR¹², CONR¹²R¹³, COR¹², SO₃R¹², CN, NO₂, halogen, OR¹², SR¹², NR¹²R¹³, OCOR¹² and NR¹²COR¹³,

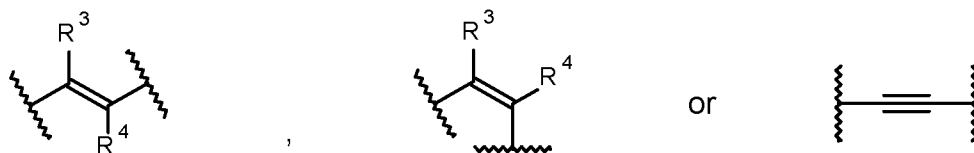
wherein R¹² and R¹³ are independently from each other and at each occurrence

C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl, and

30 wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B,

L¹ and L³ are independently from each other and at each occurrence

35



wherein

R^3 and R^4 are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl, 5 to 12 membered heteroaryl, $COOR^{20}$, $CONR^{20}R^{21}$, COR^{20} , SO_3R^{20} , CN, NO_2 , or halogen,

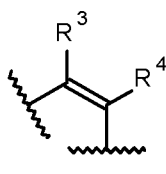
wherein R^{20} and R^{21} are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl or 5 to 12 membered heteroaryl,

wherein C_{1-20} -alkyl and C_{5-8} -cycloalkyl can be substituted with one or more substituents R^b at each occurrence selected from the group consisting of phenyl, $COOR^{22}$, $CONR^{22}R^{23}$, COR^{22} , SO_3R^{22} , CN, NO_2 , halogen, OR^{22} , SR^{22} , $NR^{22}R^{23}$, $OCOR^{22}$ and $NR^{22}COR^{23}$,

wherein C_{6-14} -aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^c at each occurrence selected from the group consisting of C_{1-10} -alkyl, cyclopentyl, cyclohexyl, $COOR^{22}$, $CONR^{22}R^{23}$, COR^{22} , SO_3R^{22} , CN, NO_2 , halogen, OR^{22} , SR^{22} , $NR^{22}R^{23}$, $OCOR^{22}$ and $NR^{22}COR^{23}$,

wherein R^{22} and R^{23} are independently from each other and at each occurrence C_{1-10} -alkyl, cyclopentyl, cyclohexyl or phenyl,

or, if L^1 or L^3 are



R^3 and R^4 together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A,

L^2 is a linking moiety A,

and

R^1 and R^2 are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl, 5 to 12 membered heteroaryl, $COOR^{30}$, $CONR^{30}R^{31}$, COR^{30} , SO_3R^{30} , CN, NO_2 , halogen, OR^{30} , SR^{30} , $NR^{30}R^{31}$, $OCOR^{30}$ or $NR^{30}COR^{31}$,

wherein R^{30} and R^{31} are independently from each other and at each occurrence H, C_{1-20} -alkyl, C_{5-8} -cycloalkyl, C_{6-14} -aryl or 5 to 12 membered heteroaryl,

wherein C_{1-20} -alkyl and C_{5-8} -cycloalkyl can be substituted with one or more substituents R^d at each occurrence selected from the group consisting of phenyl, $COOR^{32}$, $CONR^{32}R^{33}$, COR^{32} , SO_3R^{32} , CN, NO_2 , halogen, OR^{32} , SR^{32} , $NR^{32}R^{33}$, $OCOR^{32}$ and $NR^{32}COR^{33}$,

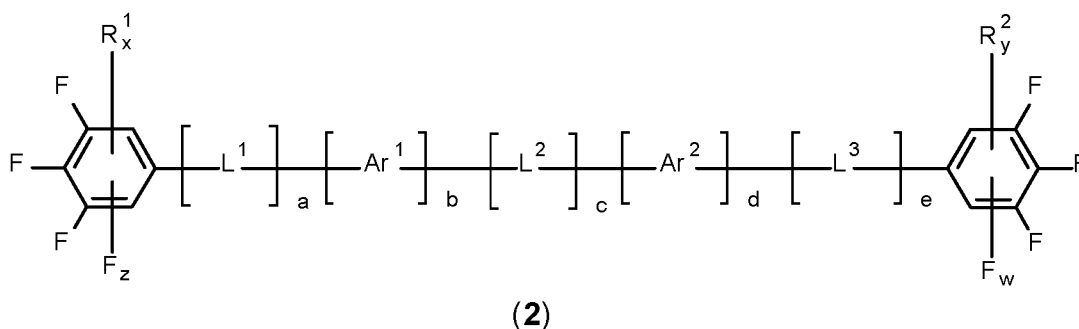
wherein C_{6-14} -aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^e at each occurrence selected from the group consisting of

C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR³², CONR³²R³³, COR³², SO₃R³², CN, NO₂, halogen, OR³², SR³², NR³²R³³, OCOR³² and NR³²COR³³,

wherein R³² and R³³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl,

5

comprises the step of reacting a compound of formula



10

wherein a, b, c, d, e, x, y, z, w, Ar¹, Ar², L¹, L³, L², R¹ and R² are as depicted for the compound of formula (1),

with M^{m+}(N₃⁻)_m,

15

wherein m is 1, 2 or 3, and M is a metal.

M can be any metal such as alkaline metal, earth alkaline metal or transition metal. Preferably, the metal is an alkaline metal, more preferably it is sodium.

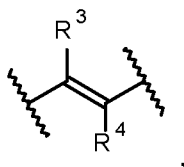
The reaction is usually performed in a solvent or solvent mixture. Preferably, the reaction is performed in a mixture of water and an organic solvent such as dimethylformamide. The reaction is usually performed at elevated temperatures such as at temperature in the range of 80 to 90 °C.

25

Depending on the type of compound of formula (2), the compound of formula (2) can be prepared by different processes.

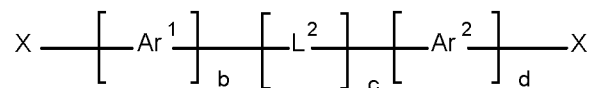
Compounds of formula (2), wherein a and e are 1, L¹ and L³ are the same and are

30



R¹ and R² are the same, x and y are the same, and z and w are the same

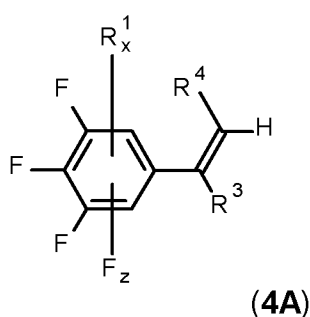
can be prepared by reacting a compound of formula



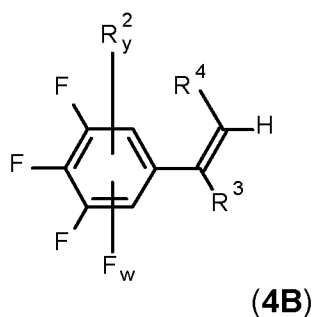
(3)

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wherein X is halogen, preferably Br, and b, c, d, Ar¹, L², Ar² are as depicted for the compound of formula (1) with compounds of formula



and



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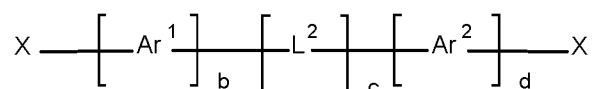
wherein x, y, z, w, R¹, R², R³ and R⁴ are as depicted for the compound of formula (1), but x and y are the same, z and w are the same and R¹ and R² are the same.

15

The reaction is usually performed in the presence of a suitable catalyst such as Pd(OAc)₂/tri(o-tolyl)phosphine. The reaction is usually performed in a suitable solvent such as dimethylformamide. The reaction is usually performed at elevated temperatures such as at a temperature in the range of 80 to 110 °C.

20

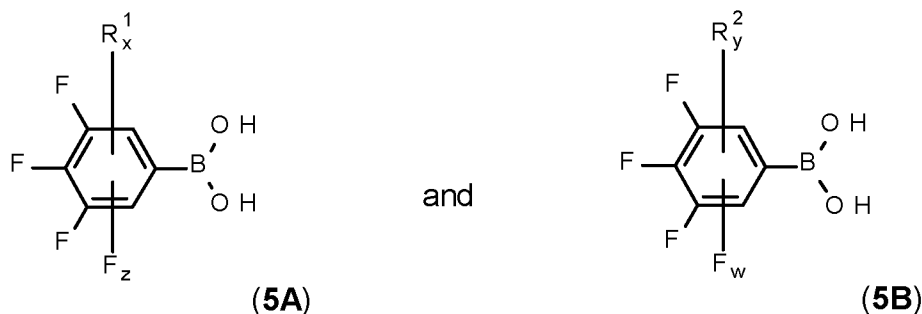
Compounds of formula (2), wherein a and e are 0, R¹ and R² are the same, x and y are the same, and z and w are the same can be prepared by reacting a compound of formula



(3)

25

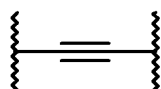
wherein X is halogen, preferably Br, and b, c, d, Ar¹, L², Ar² are as depicted for the compound of formula (1) with compounds of formula



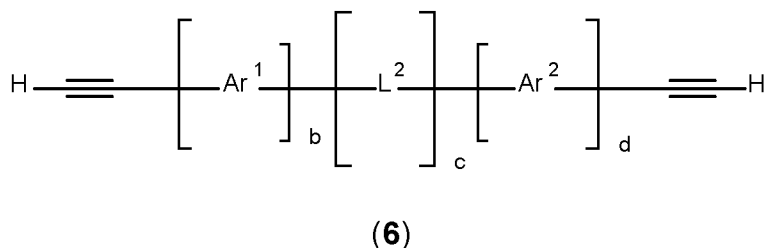
wherein x, y, z, w, R¹ and R² are as depicted for the compound of formula (1), but x and y are the same, z and w are the same and R¹ and R² are the same.

The reaction is usually performed in the presence of a suitable catalyst such as Pd(PPh₃)₄ and Ag₂O. The reaction is usually performed in a suitable solvent such as dimethylformamide. The reaction is usually performed at elevated temperatures such as at a temperature in the range of 70 to 110°C.

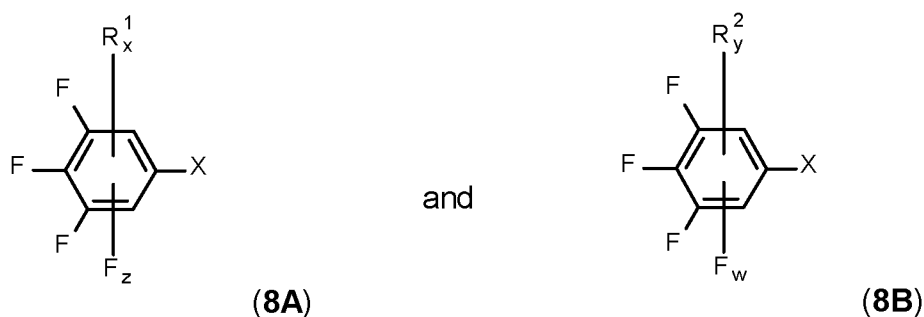
Compounds of formula (2), wherein a and e are 1, L¹ and L³ are the same and are



R¹ and R² are the same, x and y are the same, and z and w are the same can be prepared by reacting a compound of formula



wherein b, c, d, Ar¹, L², Ar² are as depicted for the compound of formula (1) with compounds of formula

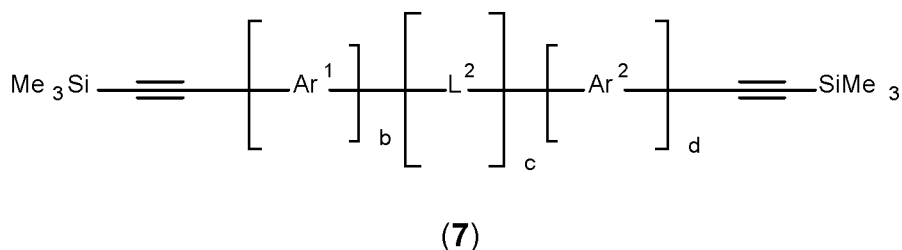


wherein X is halogen, preferably Br, x, y, z, w, R¹ and R² are as depicted for the compound of formula (1), but x and y are the same, z and w are the same and R¹ and R² are the same.

- 5 The reaction is usually performed in the presence of a suitable catalyst such as Pd(PPh₃)₂Cl₂ and CuI. The reaction is usually performed in a suitable solvent. The reaction is usually performed at elevated temperatures such as at a temperature in the range of 60 to 100°C.

The compound of formula (6) can be prepared by treating a compound of formula

10



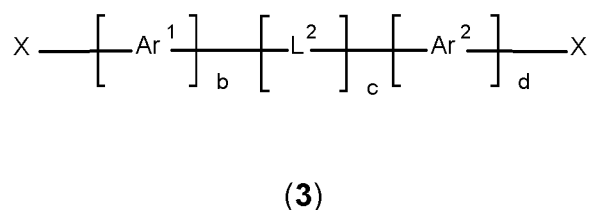
wherein b, c, d, Ar¹, Ar² and L² are as depicted for the compound of formula (1)

- 15 with a base.

The base can be potassium hydroxide. The reaction is usually performed in a suitable solvent such as tetrahydrofuran and methanol. The reaction is usually performed at ambient temperatures such as at a temperature in the range of 15 to 30 °C.

20

The compounds of formula (7) can be prepared by reacting a compound of formula

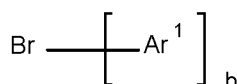


- 25 wherein b, c, d, Ar¹, Ar² and L² are as depicted for the compound of formula (1)

with ethynyltrimethylsilane.

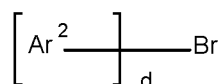
- 30 The reaction is usually performed in the presence of a suitable catalyst such as Pd(PPh₃)₂Cl₂ and CuI. The reaction is usually performed in a suitable solvent. The reaction is usually performed at elevated temperatures such as at a temperature in the range of 60 to 100°C.

The compounds of formula (3), wherein Ar¹ and Ar² are the same, b and d are 1, c is 1, X is Br and L² are as depicted for a compound of formula (1) can be prepared by reacting a compound of formula



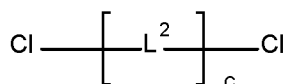
(9A)

and



(9B)

with a compound of formula



(8)

wherein c is 1 and L² is as depicted for a compound of formula (1).

Also part of the present invention is a solution comprising one or more compounds of formula (1), one or more polymers and one or more solvents.

A polymer is defined as a compound comprising at least two repeating units. Preferably, the polymer has a molecular weight of from 10'000 Da to 30 million Da. More, preferably, the polymer has a molecular weight of from 20'000 Da to 10 million Da.

The polymer can be any polymer suitable for use in an electronic device such as a dielectric polymer, a semiconductive polymer, or a polymer suitable for forming a passivation, encapsulation or planarization layer.

Preferably, the polymer is a dielectric polymer.

Examples of dielectric polymers are styrene-based polymers, poly (C₁₋₆-alkyl methacrylates) such as poly(methyl methacrylate) and poly(*tert*-butyl methacrylate), poly (C₁₋₆-alkyl acrylates), and polyimides such as the polyimides described in WO 2012/059386 and PCT/IB2013/052426.

Styrene-based polymers are polystyrene or copolymer comprising styrene units. Examples of styrene-based polymers are polystyrene, poly (4-methoxy-styrene) and styrene-butadiene block copolymers. A preferred styrene-based polymer is polystyrene.

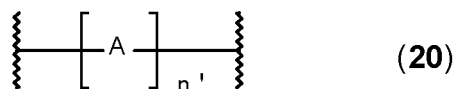
Preferably, the one or more polymers are dielectric polymers. More preferably, the one or more polymers are styrene-based polymers. Most preferably, the one or more polymers are polystyrene.

- 5 Examples of semiconducting polymers are polythiophenes such as poly 3-hexylthiophene (P3HT), polyfluorenes, polydiacetylene, poly 2,5-thienylene vinylene, poly p-phenylene vinylene (PPV) and polymers comprising repeating units having a diketopyrrolopyrrole group (DPP polymers).
- 10 Preferably the semiconducting material is a polymer comprising units having a diketopyrrolopyrrole group (DPP polymer).

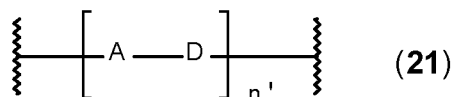
- Examples of DPP polymers and their synthesis are, for example, described in US 6,451,459 B1, WO 2005/049695, WO 2008/000664, WO 2010/049321, WO 2010/049323, WO 2010/108873,
- 15 WO 2010/115767, WO 2010/136353 and WO 2010/136352.

Preferably, the DPP polymer comprises, preferably essentially consists, of a unit selected from the group consisting of

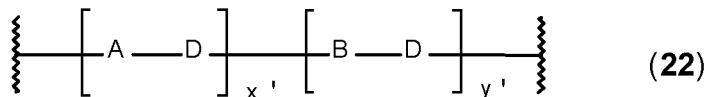
- 20 a polymer unit of formula



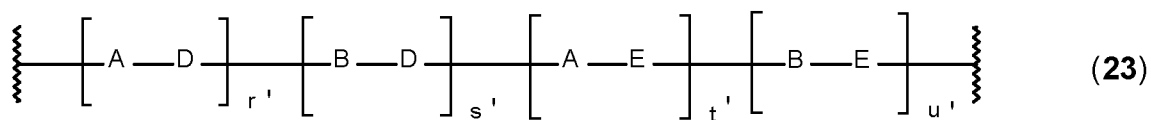
- 25 a copolymer unit of formula



- 30 a copolymer unit of formula



and a copolymer unit of formula



wherein

5 n' is 4 to 1000,

x' is 0.995 to 0.005,

y' is 0.005 to 0.995,

$x' + y' = 1$;

10

r' is 0.985 to 0.005,

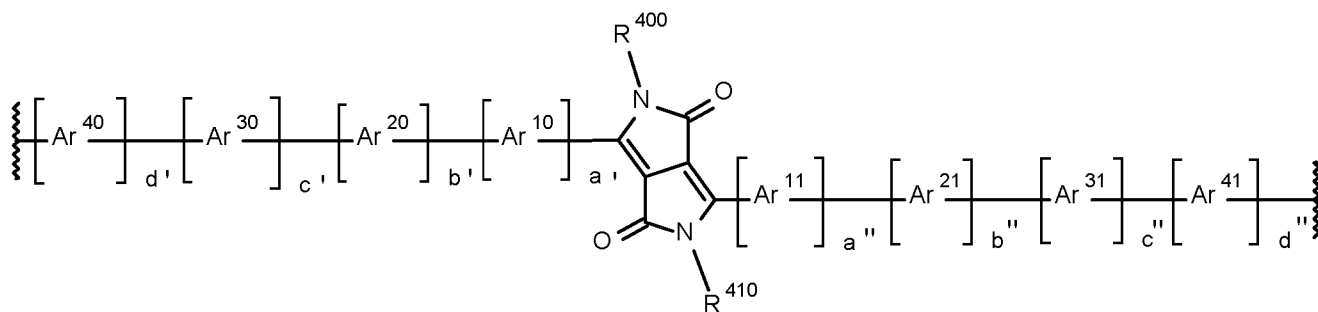
s' is 0.005 to 0.985,

t' is 0.005 to 0.985,

u' is 0.005 to 0.985,

15 $r' + s' + t' + u' = 1$;

A is a group of formula



(24)

20

wherein

25

a' is 1, 2, or 3,

a'' is 0, 1, 2, or 3,

b' is 0, 1, 2, or 3,

b'' is 0, 1, 2, or 3,

30

c' is 0, 1, 2, or 3,

c'' is 0, 1, 2, or 3,

d' is 0, 1, 2, or 3,

d'' is 0, 1, 2, or 3,
with the proviso that b'' is not 0, if a'' is 0;

R⁴⁰⁰ and R⁴¹⁰ are independently from each other selected from the group consisting of H,
C₁₋₃₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, COOR⁵⁰⁰ and C(O)NH₂,

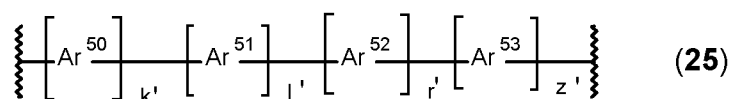
wherein R⁵⁰⁰ is C₁₋₃₀-alkyl,

wherein C₁₋₃₀-alkyl may be substituted with one or more R^k at each occurrence selected
from the group consisting of halogen, OH, NO₂, CN, C₆₋₁₄-aryl and C₅₋₈-cycloalkyl; and/or
interrupted by O, COO, OCO or S,

wherein C₅₋₈-cycloalkyl and C₆₋₁₄-aryl may be substituted with one or more R^l at each oc-
currence selected from the group consisting of C₁₋₁₀-alkyl, O-C₁₋₁₀-alkyl, S-C₁₋₁₀-alkyl and
halogen,

Ar¹⁰, Ar¹¹, Ar²⁰, Ar²¹, Ar³⁰, Ar³¹, Ar⁴⁰ and Ar⁴¹ are independently from each other a heteroaromatic or aromatic ring system,

B, D and E are independently of each other a group of formula



or a group of formula (24),

with the proviso that in case B, D and E are a group of formula (24), they are different from A,
wherein

k' is 1,

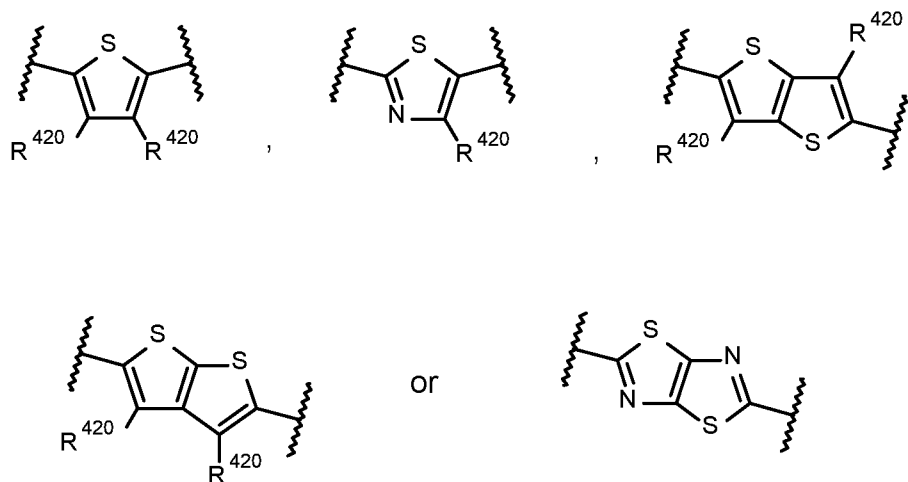
l' is 0, or 1,

r' is 0, or 1,

z' is 0, or 1, and

Ar⁵¹, Ar⁵², Ar⁵³ and Ar⁵⁴ are independently from each other a group of formula

37



wherein

R^{420} at each occurrence is H or C_{1-30} -alkyl, wherein C_{1-30} -alkyl may be interrupted by one or more O.

Preferably,

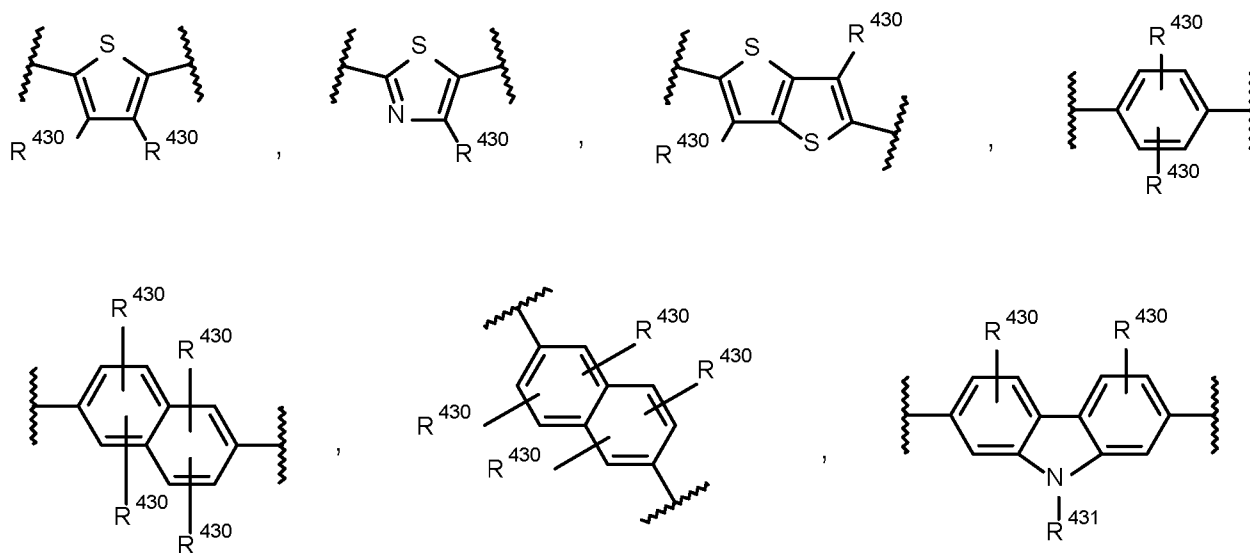
n' is 4 to 200, more preferably 5 to 100,

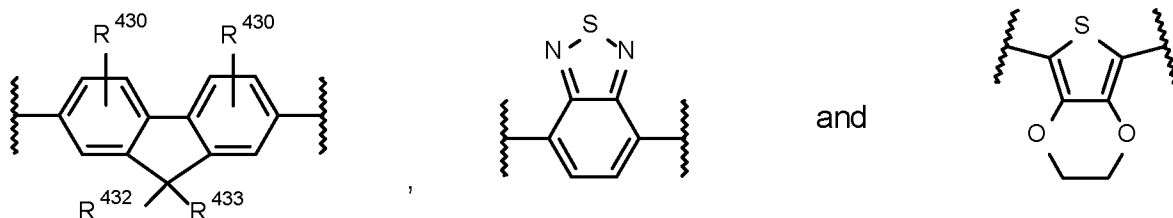
x' is 0.2 to 0.8,

y' is 0.8 to 0.2, and

$x' + y' = 1$.

Preferably, Ar^{10} , Ar^{20} , Ar^{30} , Ar^{40} , Ar^{11} , Ar^{21} , Ar^{31} and Ar^{41} are independently from each other heteroaromatic or aromatic ring systems selected from the group consisting of





and

- 5 wherein
 R^{430} is at each occurrence H, C_{1-30} -alkyl, halogen or $O-C_{1-30}$ -alkyl,
 wherein C_{1-30} -alkyl may be substituted with one or more C_{6-14} -aryl or C_{5-8} -cycloalkyl, and/or
 interrupted by one or more O or S,
- 10 R^{431} is C_{1-30} -alkyl, C_{6-14} -aryl, $O-C_{1-30}$ -alkyl or $COOR^{440}$,
 wherein R^{440} is C_{1-30} -alkyl,
 wherein C_{1-30} -alkyl may be substituted with phenyl, halogen or $COOR^{441}$, and/or interrupt-
 ed by one or more o or S,
 wherein C_{6-14} -aryl may be substituted with C_{1-10} -alkyl, C_{1-10} -perhalogenoalkyl or
 15 OC_{1-10} -alkyl, and
- R^{432} and R^{433} are independently from each other H, C_{1-30} -alkyl, C_{6-14} -aryl, 5 to 12 membered
 heteroaryl, C_{2-10} -alkenyl, C_{2-10} -alkynyl or $O-C_{1-30}$ -alkyl,
 wherein C_{1-30} -alkyl and $O-C_{1-30}$ -alkyl may be substituted with one or more substituents R^m
 20 at each occurrence selected from the group consisting of phenyl, $S-C_{1-10}$ -alkyl, $O-C_{1-10}$ -
 alkyl, CN, $NR^{441}R^{442}$, $CONR^{441}R^{442}$ and halogen; and/or interrupted by one or more CO,
 COO, S, O or NR^{443} ,
- wherein C_{6-14} -aryl and 5 to 12 membered heteroaryl may be substituted with one or more
 25 substituents R^n at each occurrence selected from the group consisting of C_{1-10} -alkyl, $S-C_{1-10}$ -
 alkyl, $O-C_{1-10}$ -alkyl, CN, $NR^{441}R^{442}$, $CONR^{441}R^{442}$ and halogen;
 wherein R^{441} , R^{442} and R^{443} are independently from each other H, C_{1-10} -alkyl or phenyl,
- or
- 30 R^{432} and R^{433} together form a group of formula $CR^{450}R^{451}$,
 wherein R^{450} and R^{451} are independently from each other H, C_{1-30} -alkyl, C_{6-14} -aryl or 5 to
 12 membered heteroaryl,
 wherein C_{1-30} -alkyl may be substituted with one or more substituents R^p at each occur-
 35 rence selected from the group consisting of phenyl, $S-C_{1-10}$ -alkyl, $O-C_{1-10}$ -alkyl, CN,
 $NR^{452}R^{453}$, $CONR^{452}R^{453}$ and halogen; and/or interrupted by one or more CO, COO, S, O
 or NR^{454} ,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl may be substituted with one or more substituents R^q at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, S-C₁₋₁₀-alkyl, O-C₁₋₁₀-alkyl, CN, NR⁴⁵²R⁴⁵³, CONR⁴⁵²R⁴⁵³ and halogen;

wherein R⁴⁵², R⁴⁵³ and R⁴⁵⁴ are independently from each other H, C₁₋₁₀-alkyl or phenyl,

or

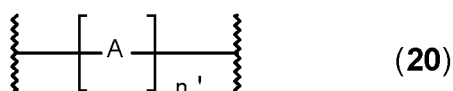
R⁴³² and R⁴³³ together with the C-atom, to which they are attached, form a five or six-membered ring, wherein the five to six-membered ring may be substituted with one or more substituents R^r selected from the group consisting of C₁₋₃₀-alkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, C₂₋₁₀-alkenyl, C₂₋₁₀-alkynyl and O-C₁₋₃₀-alkyl,

wherein C₁₋₃₀-alkyl and O-C₁₋₃₀-alkyl may be substituted with one or more substituents R^s at each occurrence selected from the group consisting of phenyl, S-C₁₋₁₀-alkyl, O-C₁₋₁₀-alkyl, CN, NR⁴⁶⁰R⁴⁶¹, CONR⁴⁶⁰R⁴⁶¹ and halogen; and/or interrupted by one or more CO, COO, S, O or NR⁴⁶²,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl may be substituted with one or more substituents R^t at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, S-C₁₋₁₀-alkyl, O-C₁₋₁₀-alkyl, CN, NR⁴⁶⁰R⁴⁶¹, CONR⁴⁶⁰R⁴⁶¹ and halogen;

wherein R⁴⁶⁰, R⁴⁶¹ and R⁴⁶² are independently from each other H, C₁₋₁₀-alkyl or phenyl.

More preferably, the DPP polymer comprises, preferably essentially consists, of a unit selected from the group consisting of a polymer unit of formula

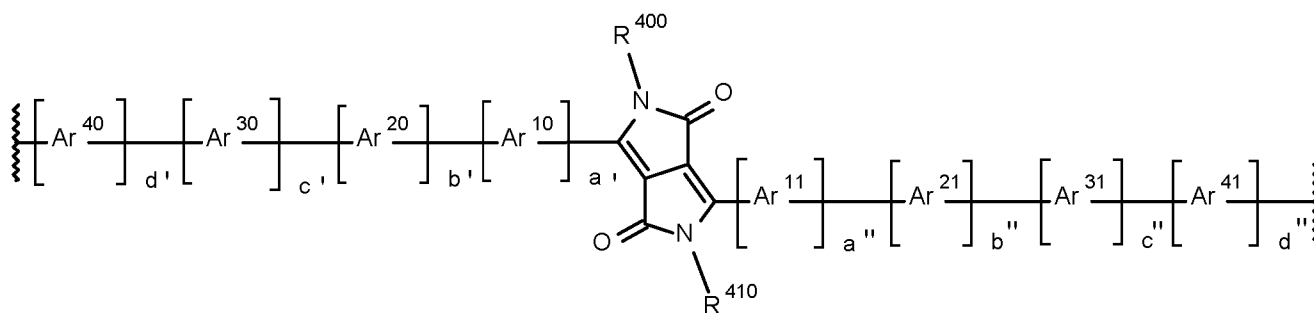


wherein

n' is 4 to 100, and

A is a group of formula

40



(24)

wherein

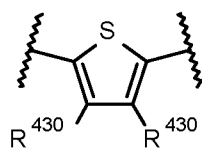
a' is 1,

a'' is 2

b', b'', c', c'', d' and d'' are 0,

R⁴⁰⁰ and R⁴¹⁰ are independently from each other C₁₋₃₀-alkyl, and

Ar¹⁰ and Ar¹¹ are heteroaromatic or aromatic ring systems, which are



wherein

R⁴³⁰ is at each occurrence H.

Preferably, the solution comprises one or more compounds of formula (1), one or more polymers and one or more solvents, wherein the solution comprises

- i) 0.1 to 500 mg of the one or more polymers in 1 ml of the composition, and
- ii) 0.1 to 20% by weight of the one or more compounds of formula (1) based on the weight of the one or more polymers.

More preferably, the solution comprises one or more compounds of formula (1), one or more polymers and one or more solvents, wherein the solution comprises

- i) 1.0 to 250 mg of the one or more polymers in 1 ml of the composition, and
- ii) 0.5 to 15% by weight of the one or more compounds of formula (1) based on the weight of the one or more polymers.

Most preferably, the solution comprises one or more compounds of formula (1), one or more polymers and one or more solvents, wherein the solution comprises

- i) 5 to 100 mg of the one or more polymers in 1 ml of the composition, and

- ii) 1 to 10% by weight of the one or more compounds of formula (1) based on the weight of the one or more polymers.

In particular, the solution comprises one or more compounds of formula (1), one or more polymers and one or more solvents, wherein the solution comprises

- i) 5 to 60 mg of the one or more polymers in 1 ml of the composition, and
ii) 2 to 8% by weight of the one or more compounds of formula (1) based on the weight of the one or more polymers.

If the polymer is polystyrene, the solvent is preferably a C₁₋₁₀-alkyl C₁₋₁₀-alkanoate such as butyl acetate.

If the polymer is a DPP polymer, the solvent is preferably an aromatic solvent such as toluene.

Also part of the present invention is a process for the preparation of a device which process comprises the steps of (i) depositing the solution of the present invention on a support in order to form a layer, and (ii) exposing the layer of step (i) to radiation in order to form a polymer layer.

Preferably, the device is an electronic device. Examples of electronic devices are light emitting diode (LED) devices, field effect transistor (FET) devices, photovoltaic (PV) devices, photodetector devices, sensing devices and radio-frequency identification (RFID) tags.

More preferably, the device is a light emitting diode (LED) device, a field effect transistor (FET) device or a photovoltaic (PV) device.

Most preferably, the device is a field effect transistor (FET) device.

A field effect transistor (FET) device comprises a dielectric layer, a semiconducting layer, a substrate, gate electrodes and source/drain electrodes.

If the device of the present invention is a field effect transistor (FET) device, the polymer layer may be the semiconducting layer or the dielectric layer. Preferably, it is the dielectric layer.

If the polymer layer is the dielectric layer, the semiconducting layer of the polymer field effect transistor (FET) device can be formed from one or more semiconducting polymers mentioned above or alternatively from small molecules. Preferably, it is formed from one or more DPP polymers.

If the polymer layer is the semiconducting layer, the dielectric layer of the field effect transistor (FET) device can be formed from one or more dielectric polymers mentioned above or alternatively from small molecules. Preferably, it is formed from one or more styrene-based polymers.

The dielectric layer can have a thickness of 5 to 2000 nm, preferably of 10 to 1000 nm.

The semiconducting layer can have a thickness of 5 to 2000 nm, preferably of 10 to 1000 nm.

- 5 The substrate can be any suitable substrate such as glass, or a plastic substrate such as polyethersulfone, polycarbonate, polysulfone, polyethylene terephthalate and polyethylene naphthalate.

- 10 The gate electrodes as well as the source/drain electrodes can be formed from any suitable metal such as gold, silver, tantalum, aluminium, tungsten or indium tin oxide. The gate electrodes as well as the source/drain electrodes can have a thickness of 1 to 200 nm, preferably from 5 to 100 nm.

A field effect transistor (FET) device can have various designs.

- 15 One possible design of a field effect transistor (FET) device is the bottom-gate, bottom-contact design. This design is depicted in Figure 9.

- 20 Another possible design of a field effect transistor (FET) device is the top-gate, bottom-contact design. This design is depicted in Figure 10.

The support depends on the and on the one or more polymers of the solution of the present invention.

- 25 If the device is a top gate, bottom contact polymer field effect transistor (FET) device and the one or more polymers are dielectric polymers, the support is the semiconducting layer of the FET.

- 30 If the device is a top gate, bottom contact polymer field effect transistor (FET) device and the one or more polymers are semiconducting polymers, the support is the substrate of the FET.

- 35 The solution of the present invention can be deposited on the support in various ways. Preferably, the solution is deposited by way of liquid processing techniques such as spin coating, solution casting, ink-jet, flexo-printing, gravure printing or slot die coating.

- Preferably, the layer of step (i) is heated to a temperature in the range of 50 to 150 °C before step (ii). More preferably, the layer of step (i) is heated to a temperature in the range of 80 to 130 °C before step (ii).

- 40 Preferably, the radiation of step (ii) has a wavelength in the range of 300 to 450 nm. For example, the radiation can have a wavelength of 365 nm, 405 nm or 436 nm.

The radiation dosage of the radiation used in step (ii) can be in the range of 1 to 1000 mJ/cm². Preferably it is in the range of 5 to 300 mJ/cm², most preferably in the range of 10 to 100 mJ/cm².

- 5 Step (ii) can be performed under inert gas atmosphere such as nitrogen or argon atmosphere.

A temperature in the range of 50 to 150 °, in particular in the range of 80 to 130 °C, can be applied during step (ii).

- 10 For example, if the polymer layer is the dielectric layer and the device is a top-gate, bottom contact field effect transistor (FET) device, the device can be prepared as follows: The source and drain electrodes can be formed by lithographically patterning a suitable source/drain material, for example gold, on a suitable substrate, for example glass. The source/drain electrodes can then be covered with a semiconducting layer by spin-coating a solution of a semiconducting
15 polymer, for example a DPP polymer, in a suitable solvent, for example toluene, on the substrate. The wet semiconducting layer can be heated. The semiconducting layer can then be covered with a dielectric layer by spin-coating a solution comprising one or more compounds of formula (1) of the present invention, one or more dielectric polymers, for example polystyrene, in a suitable solvent, for example butyl acetate, on the semiconducting layer. The wet dielectric
20 layer can be heated to 80 to 100 °C, and then cured by radiation. The gate electrode can then be deposited on the dielectric layer for example by vapour deposition of a suitable source/drain material, for example gold.

- 25 Also part of the present invention is a device obtainable by the process of the present invention.

Also part of the invention is the use of the compounds of formula (1) as cross-linkers for cross-linking one or more polymers.

- 30 The compounds of formula (1) of the present invention are advantageous in that the compounds of formula (1) absorb at a wavelength in the range of 300 to 450 nm. In particular, the compounds can be activated at a wavelength of 365 nm, 405 nm or 436 nm, which are the wavelengths currently used in industrial photolithography processes used in the preparation of devices such as control field effect transistors (FET) for displays. The compounds of formula (1) allow
35 the preparation of devices using the same wavelength for the photolithography as well as for the crosslinking of the polymer layer. Thus, there is no need to adjust the wavelength of the photo-device or even to replace the photo-device by a radiation device suitable for cross-linking the polymer during the preparation process of the device.

- 40 The compounds of formula (1) are advantageous in that they are efficient cross-linkers at wavelengths in the range of 300 to 450 nm, even when using a low radiation dosage, for example a radiation dosage in the range of 5 to 300 mJ/cm² or in the range of 10 to 100 mJ/cm². The com-

pounds of formula (1) are in particular efficient cross-linkers for dielectric layers such as polystyrene-based polymer layers. After cross-linking the polymer layer is almost not soluble in the solvent anymore used for applying the layer. Thus, the next layer, for example an electrode material layer or barrier layer, can be applied without dissolving the polymer layer. The efficient cross-linking of the compounds of formula (1) also allows the structuring (patterning) of the polymer layer using a photo-mask.

In addition, the compounds of formula (1) are soluble in organic solvents and organic solvents are usually used in the preparation of devices. Depending on the polymer layer to be applied, the compounds of formula (1) can be selected in order to be soluble in the solvent used for the polymer layer to be applied. For example, if the solvent is a more polar organic solvent such as butyl acetate, a compound of formula (1) is ideally selected, wherein Ar^1 and Ar^2 are substituted with one or more substituent C_{1-20} -alkyl in order to increase the solubility in the more polar organic solvent.

Figure 1 shows the drain current I_{ds} in relation to the gate voltage V_{gs} (transfer curve) for the top-gate, bottom-contact (TGBC) field effect transistor of example 6 comprising a dielectric layer formed from Formulation B at a source voltage V_{ds} of -3V (triangle), respectively, -30V (square).

Figure 2 shows the drain current I_{ds} in relation to the drain voltage V_{ds} (output curve) for the top-gate, bottom-contact (TGBC) field effect transistor of example 6 comprising a dielectric layer formed from Formulation B at a gate voltage V_{gs} of 5V, 0 V, -5 V, -10 V, -15 V, -20V, -25V and -30 V.

Figure 3 shows the drain current I_{ds} in relation to the gate voltage V_{gs} (transfer curve) for the top-gate, bottom-contact (TGBC) field effect transistor of example 7 comprising a dielectric layer formed from Formulation C at a source voltage V_{ds} of -3V (triangle), respectively, -30V (square).

Figure 4 shows the drain current I_{ds} in relation to the drain voltage V_{ds} (output curve) for the top-gate, bottom-contact (TGBC) field effect transistor of example 7 comprising a dielectric layer formed from Formulation C at a gate voltage V_{gs} of 5V, 0 V, -5 V, -10 V, -15 V, -20V, -25V and -30 V.

Figure 5 shows the drain current I_{ds} in relation to the gate voltage V_{gs} (transfer curve) for the top-gate, bottom-contact (TGBC) field effect transistor of example 8 comprising a semiconducting layer formed from Formulation E at a source voltage V_{ds} of -3V (triangle), respectively, -30V (square).

Figure 6 shows the drain current I_{ds} in relation to the drain voltage V_{ds} (output curve) for the top-gate, bottom-contact (TGBC) field effect transistor of example 8 comprising a semiconducting layer formed from Formulation E at a gate voltage V_{gs} of 5V, 0 V, -5 V, -10 V, -15 V, -20V, -25V and -30 V.

Figure 7 shows a microscope image of the photo-patterned dielectric layer of example 9 formed from Formulation C taken using an Axio Imager Microscope.

- 5 Figure 8 shows a microscope image of the photo-patterned semiconductor layer of example 10 formed from Formulation D taken using an Axio Imager Microscope.

Figure 9 shows the bottom-gate, bottom-contact design of a field effect transistor (FET) device.

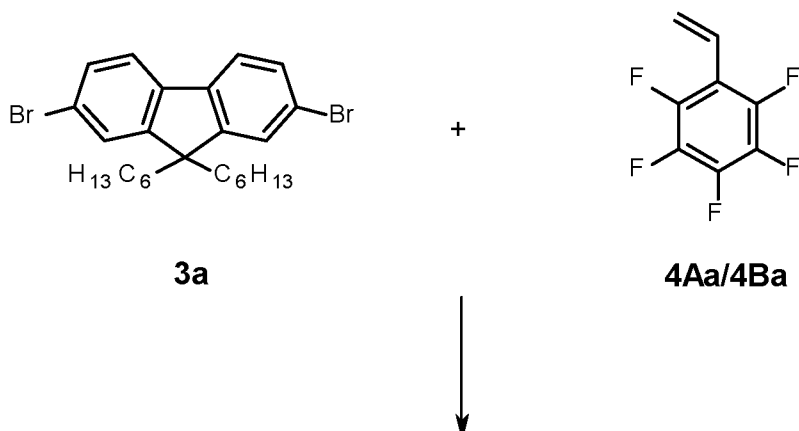
- 10 Figure 10 shows the top-gate, bottom-contact design of a field effect transistor (FET) device.

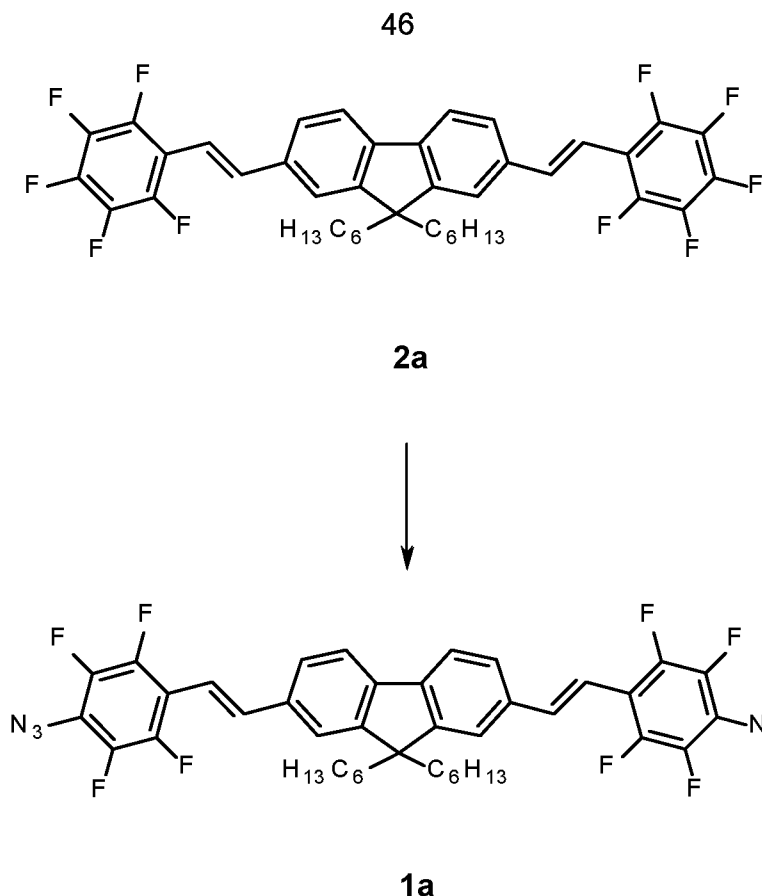
Figure 11 shows the film retention ratio (d_1/d_2) in correlation to the applied dosage of radiation for a polymer dielectric layer formed from formulation C.

15

Example 1

- 20 Preparation of compound 1a





Preparation of compound 2a

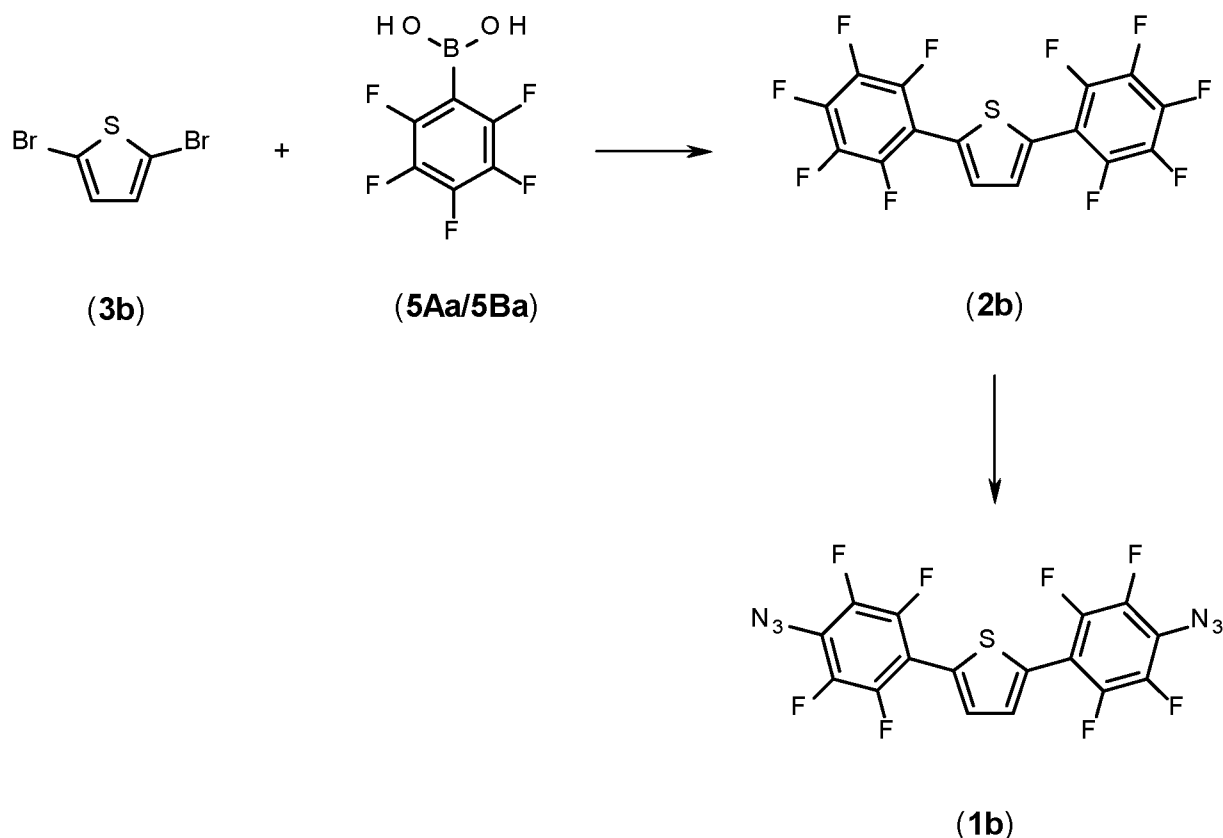
A mixture of 2,7-dibromo-9,9-dihexyl-9H-fluorene (**3a**) (492 mg, 1.00 mmol), 2,3,4,5,6-pentafluorostyrene (**4Aa/4Ba**) (524 mg, 2.7 mmol), $P(o\text{-tolyl})_3$ (12 mg, 0.04 mmol) and $\text{Pd}(\text{OAc})_2$ (4.5 mg, 0.02 mmol) in triethylamine (0.87 mL) was heated at 90 °C for 1 day under N_2 . The reaction mixture was cooled to room temperature and extracted with dichloromethane (3 x 15 mL). The organic layer was finally washed with water (3 x 30 mL). The organic phase was then dried over MgSO_4 and evaporated under reduced pressure. The crude product was purified by column chromatography using hexane as the eluent to yield compound **2a** as pale yellow solid (370 mg, 64%).

Preparation of compound 1a

A mixture of NaN_3 (73 mg, 1.1 mmol) and compound **2a** (367 mg, 0.5 mmol) in DMF (9.0 mL) and water (1.4 mL) was heated at 90 °C until no more starting material was monitored by TLC. The reaction mixture was cooled to room temperature, diluted with water, extracted with ethyl acetate and washed with water (3 x 30 mL). The organic layer was dried over MgSO_4 and the solvent removed under reduced pressure. The solid was purified by column chromatography (dichloromethane : hexane 5 : 95) to yield compound **1a** as orange solid (115 mg, 35%). $\lambda_{\text{max}} = 386$ and 408 nm.

Example 2

Preparation of compound 1b



5

Preparation of compound 2b

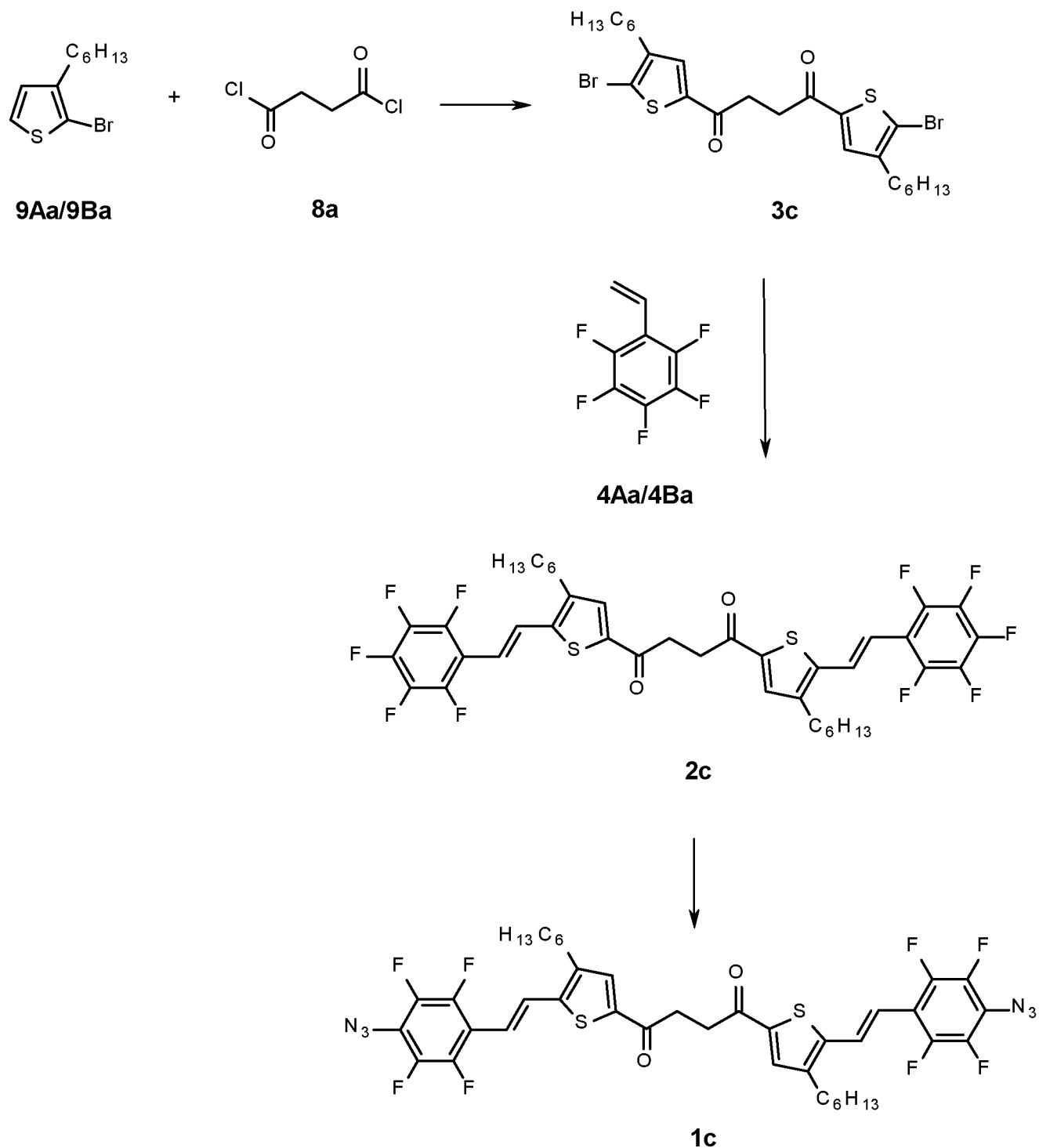
A mixture of 2,5-dibromothiophene (**3b**) (1.0 g, 4.1 mmol), 2,3,4,5,6-pentafluorophenylboronic acid (**5Aa/5Ba**) (2.1 g, 10.3 mmol), Pd(PPh₃)₄ (763 mg, 0.7 mmol), Ag₂O (1.9 g, 8.2 mmol) and K₃PO₄ trihydrate (7.025 g) in DMF (30 mL) was stirred at 85 °C, overnight. The mixture was then filtered through Celite, poured into water and extracted with dichloromethane (3 x 25 mL). The combined organic layers were washed with water (3 times), dried over MgSO₄ and the solvent was removed under reduced pressure. The crude product was purified by column chromatography using hexane as eluent to yield compound **2b** as white powder (767 mg, 45%).

15 *Preparation of compound 1b*

A mixture of NaN₃ (171 mg, 2.6 mmol) and compound **2b** (500 mg, 1.2 mmol) in DMF (20 mL) and water (3 mL) was heated at 90 °C. The reaction was monitored by TLC. The mixture was cooled to room temperature, diluted with water, extracted with ethyl acetate and washed with water (3 x 25 mL). The extract was dried over MgSO₄ and the solvent removed under reduced pressure. The crude product was purified by column chromatography with gradient elution (hexane to hexane/dichloromethane 75:25) to yield compound **1b** as a brownish-orange solid (382 mg, 69%). λ_{max} = 386 nm.

Example 3

Preparation of compound 1c



5

Preparation of compound 3c

A mixture of 2-bromo-3-hexylthiophene (**9Aa/9Ba**) (3.0 mL, 14.8 mmol) and succinyl chloride (**8a**) (0.73 mL, 6.4 mmol) in anhydrous DCM (5 mL) was added dropwise to a cooled (0 °C) suspension of AlCl_3 (2.1 g, 15.5 mmol) in anhydrous DCM (5 mL). The reaction mixture was then stirred at room temperature for 2.5 h and finally refluxed for 30 mins. The reaction mixture

10

was poured into ice followed by addition of concentrated HCl and stirred for 1h. The aqueous layer was extracted with DCM (3 x 30 mL), washed with HCl solution (10%), water, and saturated NaHCO₃ solution. Finally, the organic layer was dried over Na₂SO₄ and the solvent removed under reduced pressure. The crude solid was purified by washing with hot ethanol giving compound **3c** as orange solid (0.87 g, yield: 30%).

Preparation of compound **2c**

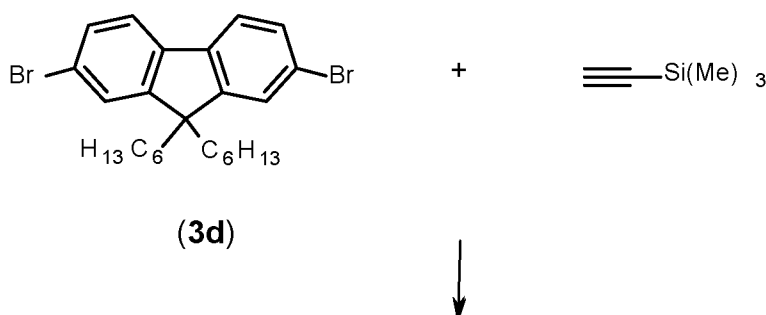
A mixture of compound **3c** (0.6 g, 1.0 mmol), 2,3,4,5,6-pentafluorostyrene (**4Aa/4Ba**) (0.4 mL, 2.7 mmol, Pd(OAc)₂ (6 mg, 0.02 mmol) and tri(o-tolyl)phosphine (0.015 g, 0.05 mmol) in triethylamine (1.18 mL, 8.50 mmol) and DMF (3 mL) was heated at 90 °C overnight. The reaction was monitored by TLC and LC/MS and heated until no more starting material was observed. Triethylamine was removed under reduced pressure and the reaction mixture was extracted with DCM (3 x 30 mL). The organic layer was washed with water (100 mL) and brine (100 mL), dried over MgSO₄ and the solvent removed under reduced pressure. The crude was purified by column chromatography using hexane/DCM (1:1) as eluent giving compound **2c** as orange solid (0.17 g, yield 26%).

Preparation of compound **1c**

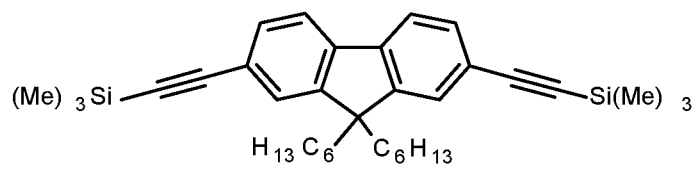
Compound **2c** (150 mg, 0.2 mmol) was dissolved in DMF (3.50 mL) and sodium azide (90 mg, 1.5 mmol) in water (0.50 mL) was subsequently added. The reaction mixture was heated at 90 °C for 3 h and monitored by TLC. Water was added to the reaction mixture which was extracted with ethyl acetate (3 x 25mL) and dried over MgSO₄. After removing the solvent under reduced pressure, the crude product was purified by column chromatography DCM/methanol (10:1) as eluent. Finally, compound **1c** was precipitated in hexane obtaining a red precipitate. The solid was filtered on a Buchner filter in to yield compound **1c** in 20% yield. $\lambda_{\max} = 405 \text{ nm}$

Example 4

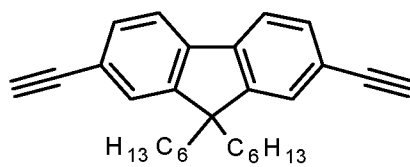
Preparation of compound **1d**



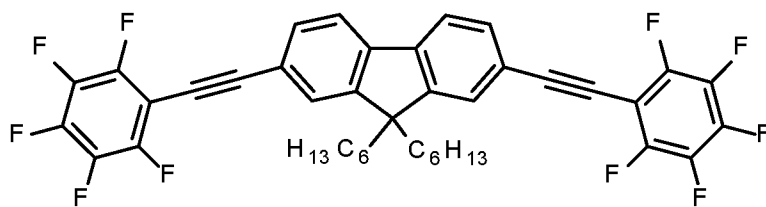
50



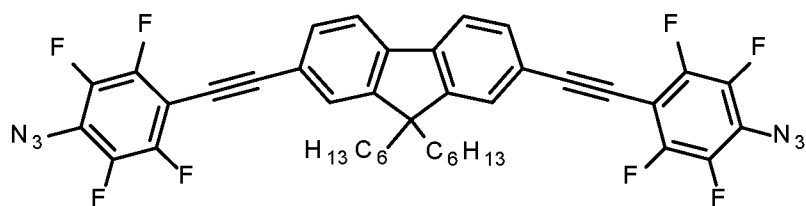
(7a)



(6a)



(2d)



(1d)

Preparation of compound 7a

A solution of ethynyltrimethylsilane (0.60 mL, 4.25 mmol) in triethylamine (8 mL) was slowly added to a solution of compound **3d** (1.0 g, 1.93 mmol), (PPh₃)₂PdCl₂ (0.068 g, 0.10 mmol), and copper iodide (0.02 g, 0.10 mmol) in triethylamine (20 mL). The resulting mixture was heated at 70°C, overnight. The reaction was monitored by TLC using hexanes as the eluent. Work up: triethylamine was evaporated under reduced pressure and the residue was purified by column chromatography over silica gel, giving compound **7a** as yellow solid in 95% yield (0.97g, 1.8 mmol).

Preparation of compound 6a

A 20% KOH aqueous solution (2.50 mL) was diluted with methanol (10 mL) and added to a solution of compound **7a** (0.97 g, 1.75 mmol) in THF (18 mL). The reaction mixture was then stirred at room temperature until no more starting material was observed by TLC (eluent hexanes). The crude reaction mixture was extracted with hexane (3 x 15mL) and the organic phase was washed with water (1 x 25 mL), and dried over Na₂SO₄. After removing the solvent under reduced pressure, the residue was then purified by column chromatography using hexanes as the eluent, giving compound **6a** as yellow oil in quantitative yield (0.7g, 1.8 mmol) that was directly used in the following step without any further purification.

Preparation of compound 2d

A solution of compound **6a** (0.20 g, 0.50 mmol) in triethylamine (1 mL) was slowly added to a solution of bromo-pentafluorobenzene (**4Aa/4Ba**) (0.14 mL, 1.09 mmol), (PPh₃)₂PdCl₂ (0.017 g, 0.02 mmol), and copper iodide (0.005 g, 0.02 mmol) in triethylamine (11 mL). The reaction mixture was then heated at 70 °C overnight and monitored by TLC. Work up: triethylamine was removed under reduced pressure and the residue was purified by column chromatography over silica gel (eluent hexanes), giving compound **2d** as white solid in 59% yield (0.21g, 0.29 mmol).

Preparation of compound 1d

Sodium azide (0.15 g, 2.30 mmol) in water (1 mL) was added to a DMF solution (5 mL) of compound **2d** (0.21 g, 0.29 mmol) and the mixture heated at 90 °C for 3hrs. Workup: water was added to the reaction mixture which was subsequently extracted with ethyl acetate (3 x 10 mL). The organic phase were gathered and dried over MgSO₄. After removing the solvent under reduced pressure the residue was purified by column chromatography over silica gel (eluent hexanes), giving compound **1d** as yellow solid in 50% yield (0.11g, 0.15 mmol). $\lambda_{\text{max}} \approx 365 \text{ nm}$.

Example 5

Preparation of Formulations A, B, C, D and E

Formulation A is a solution of 40 mg/ml polystyrene (Mw~2,000,000, supplied by Pressure Chemicals) in butyl acetate/toluene (23/2 by volume) containing in addition 2% by weight of compound **1b** based on the weight of polystyrene. Compound **1b** is prepared as described in example 2.

Formulation B is a solution of 40 mg/ml polystyrene (Mw~2,000,000, supplied by Pressure Chemicals) in butyl acetate containing in addition 4% by weight of compound **1a** based on the weight of polystyrene. Compound **1a** is prepared as described in example 1.

5

Formulation C is a solution of 40 mg/ml polystyrene (Mw~2,000,000, supplied by Pressure Chemicals) in butyl acetate containing in addition 4% by weight of compound **1d** based on the weight of polystyrene. Compound **1d** is prepared as described in example 4.

10 Formulation D is a solution of 20 mg/ml of the diketopyrrolopyrrole (DPP)-thiophene-polymer of example 1 of WO 2010/049321 in toluene containing in addition 4% by weight of compound **1b** based on the weight of the diketopyrrolopyrrole (DPP)-thiophene-polymer. Compound **1b** is prepared as described in example 2.

15 Formulation E is a solution of 0.75% by weight of the diketopyrrolopyrrole (DPP)-thiophene-polymer of example 1 of WO 2010/049321 in toluene containing in addition 4% by weight of compound **1b** based on the weight of diketopyrrolopyrrole (DPP)-thiophene-polymer. Compound **1b** is prepared as described in example 2.

20

Formulations A to E were prepared by mixing polystyrene and the diketopyrrolopyrrole (DPP)-thiophene-polymer, respectively, and the crosslinker in the solvent at room temperature.

25 Example 6

Preparation of a top-gate, bottom contact field effect transistor (FET) device comprising a dielectric layer formed from Formulation B

30 Gold was deposited by thermal evaporation through a shadow mask onto a glass substrate to form an approximately 60 nm thick film of source/drain electrodes (channel length: 50 μm , channel width: 500 μm). A 0.75% by weight solution of the diketopyrrolopyrrole (DPP)-thiophene-polymer of example 1 of WO 2010/049321 in toluene was filtered through a 0.45 micrometer polytetrafluoroethylene (PTFE) filter and then applied by spin coating (1000 rpm, 30 seconds). The wet semiconducting layer was dried at 90 °C on a hot plate for
35 30 seconds. Formulation B described in example 5 was filtered through a 0.45 micrometer filter and then applied by spin coating (3000 rpm, 30 seconds). The wet dielectric layer was pre-baked at 90 °C for 2 minutes on a hot plate to obtain a 520 nm thick layer. The polymer dielectric layer was UV-cured using 365 nm (radiation dosage 960 mJ/cm²) at 90 °C. Gate electrodes of gold (thickness approximately 80 nm) were evaporated through a shadow mask on the die-
40 lectric layer.

The characteristics of the top gate, bottom contact field effect transistor (FET) device were measured with a Keithley 4200-SCS semiconductor characterization system. The drain current

I_{ds} in relation to the gate voltage V_{gs} (transfer curve) for the device comprising a dielectric layer formed from Formulation B at a source voltage V_{ds} of -3V (triangle), respectively, -30V (square) is shown in Figure 1. The drain current I_{ds} in relation to the drain voltage V_{ds} (output curve) for the device comprising a dielectric layer formed from Formulation B at a gate voltage V_{gs} of 5V, 0 V, -5 V, -10 V, -15 V, -20V, -25V and -30 V is shown in Figure 2.

The results are depicted in table 1.

dielectric layer formed from	Mean mobility [cm ² /Vs]	Mean I_{on}/I_{off}	Mean V_{on} [V]	I_g [@ 30V]
Formulation B	0.135	1.13E+04	2	3.31E-08

Table 1.

Example 7

Preparation of a top-gate, bottom contact field effect transistor (FET) device comprising a dielectric layer formed from Formulation C

Gold was deposited by thermal evaporation through shadow mask onto glass substrate to form an approximately 60 nm thick film of source/drain electrodes (channel length: 50 μ m, channel width: 500 μ m). A 0.75% by weight solution of the diketopyrrolopyrrole (DPP)-thiophene-polymer of example 1 of WO 2010/049321 in toluene was filtered through a 0.45 micrometer polytetrafluoroethylene (PTFE) filter and then applied by spin coating (1000 rpm, 30 seconds). The wet semiconducting layer was dried at 90 °C on a hot plate for 30 seconds. Formulation C described in example 5 was filtered through a 0.45 micrometer filter and then applied by spin coating (3500 rpm, 30 seconds). The wet dielectric layer was pre-baked at 90 °C for 2 minutes on a hot plate to obtain a 520 nm thick layer. The dielectric layer was UV-cured using 365 nm (radiation dosage 1120 mJ/cm²) at 100 °C with nitrogen flow. Gate electrodes of gold (thickness approximately 80 nm) were evaporated through a shadow mask on the dielectric layer.

The characteristics of the top gate, bottom contact field effect transistor (FET) device were measured with a Keithley 4200-SCS semiconductor characterization system. The drain current I_{ds} in relation to the gate voltage V_{gs} (transfer curve) for the device comprising a dielectric layer formed from Formulation C at a source voltage V_{ds} of -3V (triangle), respectively, -30V (square) is shown in Figure 3. The drain current I_{ds} in relation to the drain voltage V_{ds} (output curve) for the device comprising a dielectric layer formed from Formulation C at a gate voltage V_{gs} of 5V, 0 V, -5 V, -10 V, -15 V, -20V, -25V and -30 V is shown in Figure 4.

The results are depicted in table 2.

dielectric layer formed from	Mean mobility [cm ² /Vs]	Mean I _{on} /I _{off}	Mean V _{on} [V]	I _g [@ 30V]
Formulation C	0.20	3.16E+04	1	8.67E-09

Table 2.

Example 8

- 5 Preparation of a top-gate, bottom contact polymer field effect transistor (FET) device comprising a polymer semiconducting layer formed from Formulation E

10 Gold was deposited by thermal evaporation through shadow mask onto glass substrate to form an approximately 60 nm thick film of source/drain electrodes (channel length: 50μm, channel width: 500μm). Formulation E was applied by spin coating (1000 rpm, 30 seconds). The wet polymer semiconducting layer was dried at 90 °C on a hot plate for 30 seconds, and then UV-cured using 365 nm (radiation dosage 2400 mJ/cm²) at 90 °C. A 4.0% by weight solution of polystyrene supplied by Pressure Chemicals in butyl acetate was applied by spin coating (3000 rpm, 30 seconds), and dried at 90 °C for 30 seconds. Gate electrodes of gold (thickness 15 approximately 80 nm) were evaporated through a shadow mask on the dielectric layer.

The characteristics of the top gate, bottom contact field effect transistor (FET) device were measured with a Keithley 4200-SCS semiconductor characterization system. The drain current I_{ds} in relation to the gate voltage V_{gs} (transfer curve) for the device comprising a semiconducting 20 layer formed from Formulation E at a source voltage V_{ds} of -3V (triangle), respectively, -30V (square) is shown in Figure 5. The drain current I_{ds} in relation to the drain voltage V_{ds} (output curve) for polymer device comprising a semiconducting layer formed from Formulation E at a gate voltage V_{gs} of 5V, 0 V, -5 V, -10 V, -15 V, -20V, -25V and -30 V is shown in Figure 6.

- 25 The results are depicted in table 3.

semiconducting layer formed from	Mean mobility [cm ² /Vs]	Mean I _{on} /I _{off}	Mean V _{on} [V]	I _g [@ 30V]
Formulation E	0.028	4.82E+03	2	4.47E-10

Table 3.

Example 9

Photo-patterning of a polymer dielectric layer formed from Formulation C on top of a polymer semiconducting layer

- 5 A 0.75 % by weight solution of the diketopyrrolopyrrole (DPP)-thiophene-polymer of example 1 of WO 2010/049321 in toluene was filtered through a 0.45 micrometer polytetrafluoroethylene (PTFE) filter and applied to a clean silicon dioxide substrate by spin coating (1,500 rpm, 30 seconds). The wet polymer semiconducting layer was dried at 90 °C on a hot plate for 30 seconds. Formulation C, described in example 5, was filtered through a 0.45 micrometer
10 filter and then applied on top of the polymer semiconducting layer by spin coating (3,500 rpm, 30 seconds). The wet polymer dielectric layer was pre-baked at 90 °C for 2 minutes on a hot plate to obtain a 520 nm thick layer. A shadow mask was aligned on top of the dielectric layer before curing using 365 nm (radiation dosage 60 mJ/cm²) with nitrogen flow. The cured film was developed by immersing the film into butyl acetate for 1 minute followed by blowing with nitro-
15 gen and heating at 90°C for 5 minutes.

A microscope image of the photo-patterned polymer dielectric layer formed from Formulation C taken using an Axio Imager Microscope is shown in Figure 7.

20

Example 10

Photo-patterning of a semiconductor layer formed from Formulation D

- Formulation D, described in example 5, was filtered through a 0.45 micrometer filter and then
25 applied on top of the silicon dioxide substrate by spin coating (1,500 rpm, 30 seconds). A shadow mask was aligned on top of the semiconducting layer before curing using 365 nm (radiation dosage 2400 mJ/cm²) at 90 °C. The cured film was developed by immersing the film into toluene for 1 minute followed by blowing with nitrogen and heating on a 90°C hotplate for 5
30 minutes.

A microscope image of the photo-patterned semiconductor layer formed from Formulation D taken using an Axio Imager Microscope is shown in Figure 8.

35 Example 11

Stability of the cured dielectric layer formed from Formulation A, respectively, Formulation C towards solvent dissolution

- 40 Formulation A, respectively, Formulation C, both described in example 5, was filtered through a 0.45 micrometer polytetrafluoroethylene (PTFE) filter and coated on a clean silicon dioxide substrate by spin coating (3500 rpm, 30 s). The wet dielectric layer was heated at 90°C for 2 minutes on the hotplate to obtain 550 nm thick film. The dielectric layer formed from Formulation A was UV-cured using 365 nm (radiation dosage 960 mJ/cm²) at 90 °C. The dielectric layer

formed from Formulation C was UV-cured using 365 nm (radiation dosage 1120 mJ/cm²) with nitrogen flow at 100 °C. Development of the dielectric layer was done by immersing the dielectric layer into butyl acetate for 1 minute followed by heating at 90 °C for 5 minutes. The thickness of the dielectric layer was measured after curing before development (d1) and after development (d2) using Veeco Dektak 150 to obtain the film retention ratio (d2/d1).

The results are depicted in table 4.

	dielectric layer formed from	
	Formulation A	Formulation C
Average Film Retention Ratio [%]	94	99

Table 4.

Example 12

Stability of the cured semiconducting layer formed from Formulation D towards solvent dissolution

Formulation D described in example 5, was filtered through a 0.45 micrometer polytetrafluoroethylene (PTFE) filter and coated on a clean silicon dioxide substrate by spin coating (1500 rpm, 30 s). The wet polymer semiconducting layer was heated at 90°C for 2 minutes on the hot-plate, cooled to 60 °C, and then the polymer semiconducting layer was UV-cured using 365 nm (radiation dosage ca. 2400 mJ/cm²) at 90 °C. Development of the polymer semiconducting layer was done by immersing the layer into toluene for 1 minute followed by heating at 90 °C for 5 minutes. The thickness of the polymer semiconducting layer was measured after curing before development (d1) and after development (d2) using Veeco Dektak 150 to obtain the film retention ratio (d2/d1).

The results are depicted in table 5.

	semiconducting layer formed from
	Formulation D
Average Film Retention Ratio [%]	80

Table 5.

Example 13

Preparation of capacitor comprising a dielectric layer formed from Formulation C

Formulation C, described in example 5, was filtered through a 0.45 micrometer filter and applied on a clean glass substrate pre-coated with indium tin oxide (ITO) electrodes by spin coating (3500 rpm, 30 seconds). The wet dielectric layer was pre-baked at 90 °C for 2 minutes on a hot plate to obtain a 500 nm thick layer. The dielectric layer was UV-cured using 365 nm (radiation

dosage 1120 mJ/cm²) at 100 °C with nitrogen flow. Gold electrodes (area = 0.785 mm²) were then vacuum-deposited through a shadow mask on the dielectric layer at < 1x10⁻⁶ Torr (1.3 x 10⁻⁴ Pa).

- 5 The capacitor thus obtained was characterized in the following way: The relative permittivity was deduced from the complex capacity measured with an Agilent E4980A Precision LCR Meter (signal amplitude 1 V).

The results are depicted in table 6.

10

	Relative permittivity of capacitor comprising a dielectric layer formed from	
Frequency [Hz]	pure polystyrene	Formulation C
40	2.65	2.44
4000	2.50	2.51
1000000	2.49	2.51

Table 6.

As can be derived from table 6 the dielectric constant is unaffected by the addition of compound 1d.

15

Example 14

Evaluation of the effect of the radiation dosage on the cured polymer layer

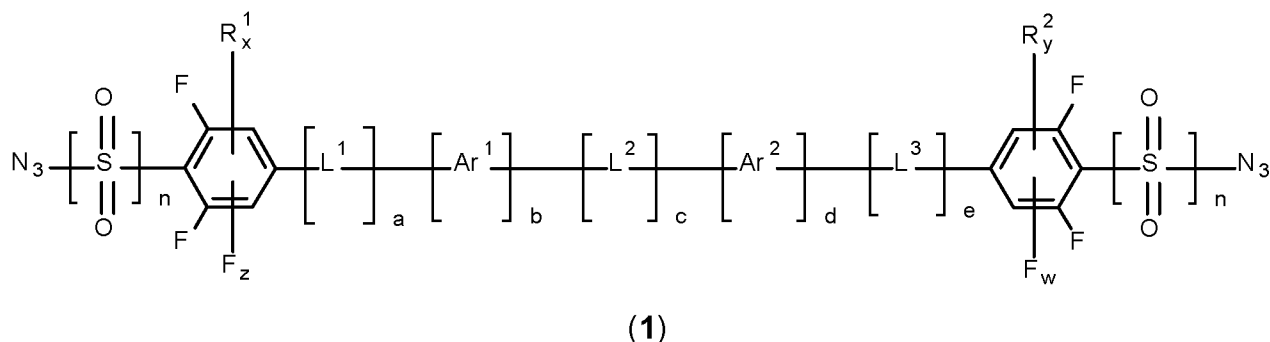
- 20 Formulation C, described in example 5, was filtered through a 0.45 micrometer filter and applied on a silicon dioxide substrate by spin coating (3500 rpm, 30 seconds). The wet dielectric layer was pre-baked at 90 °C for 2 minutes on a hot plate to obtain a 550 nm thick layer. The polymer dielectric layer was UV-cured using 365 nm with different radiation dosages using nitrogen flow. Development of the dielectric layer was done by immersing the dielectric layer into butyl acetate
 25 for 1 minute followed by heating at 90 °C for 5 minutes. The thickness of the dielectric layer was measured after curing before development (d1) and after development (d2) using Veeco Dektak 150 to obtain the film retention ratio (d2/d1).

- 30 The film retention ratio (d1/d2) in correlation to the applied dosage of radiation for a dielectric layer formed from formulation C is depicted in Figure 11.

Figure 11 shows that the applied radiation dosage can be reduced to 20 mJ/cm², and the film retention ratio is still retained above 90%.

Claims

1. Compounds of formula



5

wherein

a is 0, 1 or 2,

b is 1, 2, 3 or 4,

c is 0 or 1,

10 d is 0, 1, 2, 3 or 4,

e is 0, 1 or 2,

x is 0, 1 or 2,

y is 0, 1 or 2,

15 z is 0, 1 or 2,

w is 0, 1 or 2,

n is 0 or 1,

20 Ar¹ and Ar² are independently from each other and at each occurrence an aromatic or heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H,

25 C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^{aa} at each occurrence selected from the group consisting of phenyl, COOR¹², CONR¹²R¹³, COR¹², SO₃R¹², CN, NO₂, halogen, OR¹², SR¹², NR¹¹R¹², OCOR¹² and NR¹²COR¹³,

30 wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{ab} at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR¹², CONR¹²R¹³, COR¹², SO₃R¹², CN, NO₂, halogen, OR¹², SR¹², NR¹²R¹³, OCOR¹² and NR¹²COR¹³,

wherein R¹² and R¹³ are independently from each other and at each occurrence

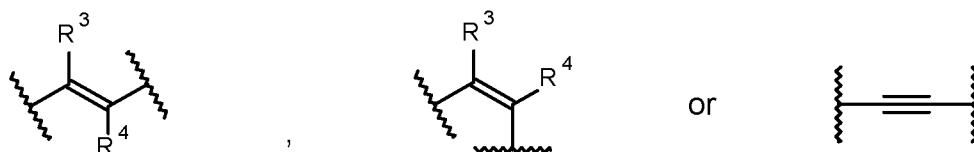
C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl, and

35

wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B,

5

L¹ and L³ are independently from each other and at each occurrence



10

wherein

R³ and R⁴ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR²⁰, CONR²⁰R²¹, COR²⁰, SO₃R²⁰, CN, NO₂, or halogen,

15

wherein R²⁰ and R²¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^b at each occurrence selected from the group consisting of phenyl, COOR²², CONR²²R²³, COR²², SO₃R²², CN, NO₂, halogen, OR²², SR²², NR²²R²³, OCOR²² and NR²²COR²³,

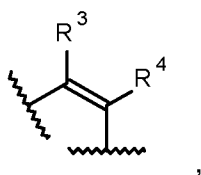
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wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^c at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR²², CONR²²R²³, COR²², SO₃R²², CN, NO₂, halogen, OR²², SR²², NR²²R²³, OCOR²² and NR²²COR²³,

25

wherein R²² and R²³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl,

or, if L¹ or L³ are



30

R³ and R⁴ together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A,

35 L² is a linking moiety A,

and

R¹ and R² are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR³⁰, CONR³⁰R³¹, COR³⁰, SO₃R³⁰, CN, NO₂, halogen, OR³⁰, SR³⁰, NR³⁰R³¹, OCOR³⁰ or NR³⁰COR³¹,

wherein R³⁰ and R³¹ are independently from each other and at each occurrence H,

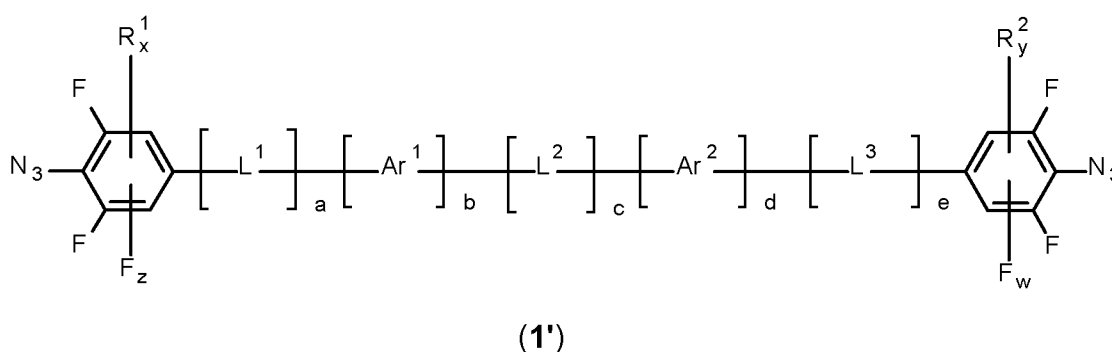
C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^d at each occurrence selected from the group consisting of phenyl, COOR³², CONR³²R³³, COR³², SO₃R³², CN, NO₂, halogen, OR³², SR³², NR³²R³³, OCOR³² and NR³²COR³³,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^e at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR³², CONR³²R³³, COR³², SO₃R³², CN, NO₂, halogen, OR³², SR³², NR³²R³³, OCOR³² and NR³²COR³³,

wherein R³² and R³³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl.

2. Compounds of claim 1, wherein n = 0, and the compound of formula (1) is of formula



wherein R¹, R², x, y, z, w, L¹, Ar¹, L², Ar², L³, a, b, c, d and e are as depicted in claim 1.

3. The compounds of claim 1 or 2, wherein

Ar¹ and Ar² are independently from each other and at each occurrence an aromatic or heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,

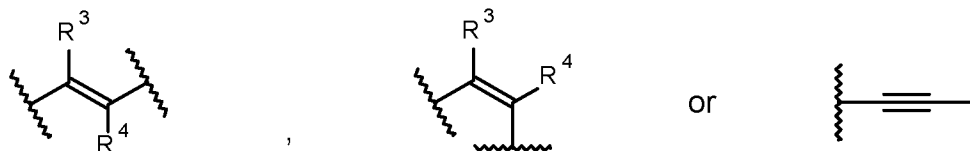
wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H,

C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, and

wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B, and

L¹ and L³ are independently from each other and at each occurrence

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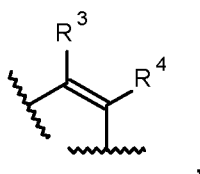


wherein

R³ and R⁴ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR²⁰, CONR²⁰R²¹, COR²⁰, SO₃R²⁰, CN, NO₂, or halogen,

wherein R²⁰ and R²¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

or, if L¹ or L³ are



R³ and R⁴ together with the C-atoms to which they are attached form a 5 to 7-membered non-aromatic ring system A,

4. The compounds of claim 1, 2 or 3, wherein

L² is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C₁₋₁₀-alkylene, C₂₋₁₀-alkenylene, C₅₋₈-cycloalkylene, C₁₋₄-alkylene-C₅₋₈-cycloalkylene-C₁₋₄-alkylene, C₁₋₄-alkylene-phenylene-C₁₋₄-alkylene, C₂₋₄-alkenylene-C₅₋₈-cycloalkylene-C₂₋₄-alkenylene and C₂₋₄-alkenylene-phenylene-C₂₋₄-alkenylene, which can be substituted with one or more substituent R^f at each occurrence selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR⁴⁰, CONR⁴⁰R⁴¹, COR⁴⁰, SO₃R⁴⁰, CN, NO₂, halogen, OR⁴⁰, SR⁴⁰, NR⁴⁰R⁴¹, OCOR⁴⁰ and NR⁴⁰COR⁴¹,

wherein R⁴⁰ and R⁴¹ are independently from each other and at each occurrence H, C₁₋₁₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

wherein C₁₋₂₀-alkyl and C₅₋₈-cycloalkyl can be substituted with one or more substituents R^{fa} at each occurrence selected from the group consisting of phenyl, COOR⁴², CONR⁴²R⁴³, COR⁴², SO₃R⁴², CN, NO₂, halogen, OR⁴², SR⁴², NR⁴²R⁴³, OCOR⁴² and NR⁴²COR⁴³,

wherein C₆₋₁₄-aryl and 5 to 12 membered heteroaryl can be substituted with one or more substituent R^{fb} at each occurrence selected from the group consisting of C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl, COOR⁴², CONR⁴²R⁴³, COR⁴², SO₃R⁴², CN, NO₂, halogen, OR⁴², SR⁴², NR⁴²R⁴³, OCOR⁴² and NR⁴²COR⁴³,

wherein R⁴² and R⁴³ are independently from each other and at each occurrence C₁₋₁₀-alkyl, cyclopentyl, cyclohexyl or phenyl, and

wherein one or more CH₂ groups of C₁₋₁₀-alkylene, C₁₋₄-alkylene, C₂₋₁₀-alkenylene, C₂₋₄-alkenylene and/or C₅₋₈-cycloalkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

- 5 wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl, and

- R¹ and R² are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR³⁰, CONR³⁰R³¹, COR³⁰, SO₃R³⁰, CN, NO₂,
 10 halogen, OR³⁰, SR³⁰, NR³⁰R³¹, OCOR³⁰ or NR³⁰COR³¹,
 wherein R³⁰ and R³¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl.

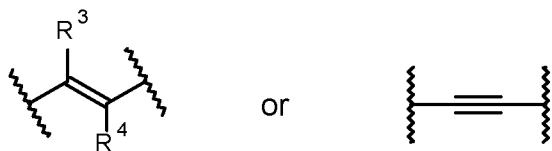
5. The compounds of any of claim 1, 2, 3 or 4, wherein
 15 a and e are the same and are 0 or 1,
 b is 1, 2 or 3,
 c is 0 or 1, and
 d is 0, 1, 2 or 3,

- 20 x and y are the same and are 0, 1 or 2, and
 z and w are the same and are 0, 1 or 2,

- Ar¹ and Ar² are independently from each other and at each occurrence a C₆₋₁₄-aromatic or a 5 to 12 membered heteroaromatic moiety, which can be substituted with one or more substituent R^a
 25 selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR¹⁰, CONR¹⁰R¹¹, COR¹⁰, SO₃R¹⁰, CN, NO₂, halogen, OR¹⁰, SR¹⁰, NR¹⁰R¹¹, OCOR¹⁰ and NR¹⁰COR¹¹,
 wherein R¹⁰ and R¹¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

- 30 wherein at least two adjacent Ar¹, at least two adjacent Ar², and/or Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B,

- 35 L¹ and L³ are the same and are



wherein

R³ and R⁴ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR²⁰, CONR²⁰R²¹, COR²⁰, SO₃R²⁰, CN, NO₂ or halogen,

5 wherein R²⁰ and R²¹ are independently from each other and at each occurrence H, C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl,

10 L² is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C₁₋₁₀-alkylene, C₂₋₁₀-alkenylene, C₅₋₈-cycloalkylene, C₁₋₄-alkylene-C₅₋₈-cycloalkylene-C₁₋₄-alkylene, C₁₋₄-alkylene-phenylene-C₁₋₄-alkylene, C₂₋₄-alkenylene-C₅₋₈-cycloalkylene-C₂₋₄-alkenylene and C₂₋₄-alkenylene-phenylene-C₂₋₄-alkenylene, which can be substituted with one or more substituent R^f at each occurrence selected from the group consisting of C₁₋₂₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl, 5 to 12 membered heteroaryl, COOR⁴⁰, CONR⁴⁰R⁴¹, COR⁴⁰, SO₃R⁴⁰, CN, NO₂, halogen, OR⁴⁰, SR⁴⁰, NR⁴⁰R⁴¹, OCOR⁴⁰ and NR⁴⁰COR⁴¹,

15 wherein R⁴⁰ and R⁴¹ are independently from each other and at each occurrence H, C₁₋₁₀-alkyl, C₅₋₈-cycloalkyl, C₆₋₁₄-aryl or 5 to 12 membered heteroaryl, and

wherein one or more CH₂ groups of C₁₋₁₀-alkylene, C₁₋₄-alkylene, C₂₋₁₀-alkenylene, C₂₋₄-alkenylene and/or C₅₋₈-cycloalkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

20 wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl, and

R¹ and R² are the same and are H, C₁₋₂₀-alkyl or C₅₋₈-cycloalkyl.

25 6. The compounds of claim 5, wherein
a and e are the same and are 0 or 1,
b is 1,
c is 0 or 1, and
d is 0 or 1,

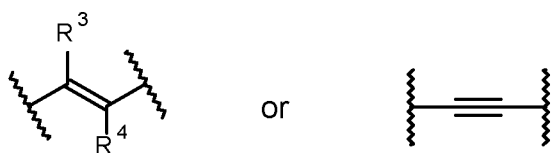
30 x and y are the same and are 0 or 1, and
z and w are the same and are 1 or 2,

35 Ar¹ and Ar² are the same and are a C₆₋₁₄-aromatic or a 5 to 12 membered heteroaromatic moiety, which can be substituted with one or more substituent R^a selected from the group consisting of C₁₋₂₀-alkyl and OR¹⁰,

wherein R¹⁰ is independently from each other and at each occurrence C₁₋₂₀-alkyl, and

40 wherein Ar¹ and Ar², both connected to L² or if c = 0 to each other, can be additionally linked by one or more L^a, wherein L^a is a linking moiety B, wherein the linking moiety B is C₁₋₄-alkylene, which can be substituted with one or more C₁₋₁₀-alkyl,

L¹ and L³ are the same and are



wherein

- 5 R^3 and R^4 are independently from each other and at each occurrence H, C_{1-20} -alkyl, $COOR^{20}$, $CONR^{20}R^{21}$, COR^{20} , SO_3R^{20} , CN, NO_2 or halogen, wherein R^{20} and R^{21} are independently from each other and at each occurrence H or C_{1-20} -alkyl,

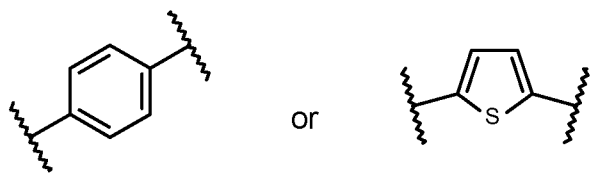
- 10 L^2 is a linking moiety A, wherein the linking moiety A is selected from the group consisting of C_{1-10} -alkylene, C_{2-10} -alkenylene, C_{5-8} -cycloalkylene, C_{1-4} -alkylene- C_{5-8} -cycloalkylene- C_{1-4} -alkylene, C_{1-4} -alkylene-phenylene- C_{1-4} -alkylene, C_{2-4} -alkenylene- C_{5-8} -cycloalkylene- C_{2-4} -alkenylene and C_{2-4} -alkenylene-phenylene- C_{2-4} -alkenylene,

- 15 wherein one or more CH_2 groups of C_{1-10} -alkylene, C_{1-4} -alkylene, C_{2-10} -alkenylene, C_{2-4} -alkenylene and/or C_{5-8} -cycloalkylene can be replaced by $C=O$, $(C=O)O$, $(C=O)NR^{50}$, SO_2-NR^{50} , NR^{50} , $NR^{50}R^{51}$, O or S, wherein R^{50} and R^{51} are independently from each other and at each occurrence C_{1-10} -alkyl, and

- 20 R^1 and R^2 are the same and are branched C_{3-6} -alkyl.

7. The compounds of claim 6, wherein
 x and y are the same and are 0,
 25 z and w are the same and are 2,

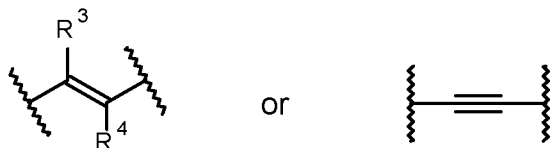
Ar^1 and Ar^2 are the same and are



- 30 which can be substituted with one or more substituent R^a selected from the group consisting of C_{1-10} -alkyl and OR^{10} , wherein R^{10} is independently from each other and at each occurrence C_{1-10} -alkyl, and

- 35 wherein Ar^1 and Ar^2 , both connected to L^2 or if $c = 0$ to each other, can be additionally linked by one or more L^a , wherein L^a is a linking moiety B, wherein the linking moiety B is methylene substituted with one or more C_{1-10} -alkyl,

L¹ and L³ are the same and are



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wherein

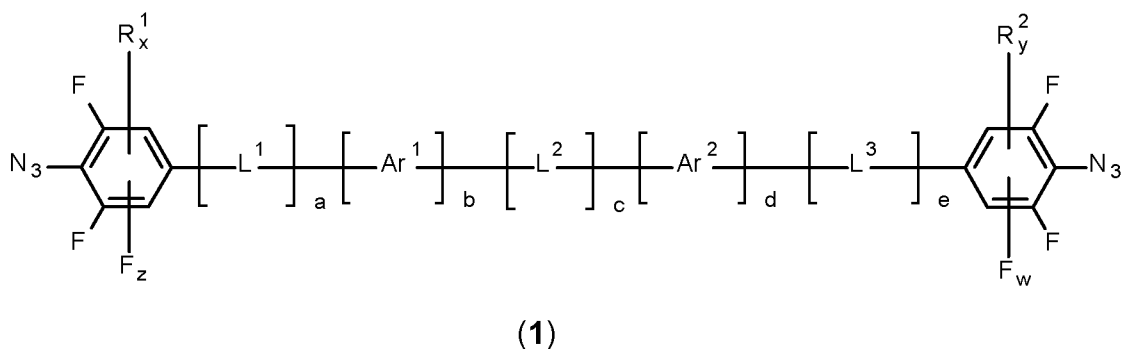
R³ and R⁴ are H, and

L² is a linking moiety A, wherein the linking moiety A is C₁₋₁₀-alkylene,

10 wherein one or more CH₂ groups of C₁₋₁₀-alkylene can be replaced by C=O, (C=O)O, (C=O)NR⁵⁰, SO₂-NR⁵⁰, NR⁵⁰, NR⁵⁰R⁵¹, O or S,

wherein R⁵⁰ and R⁵¹ are independently from each other and at each occurrence C₁₋₁₀-alkyl.

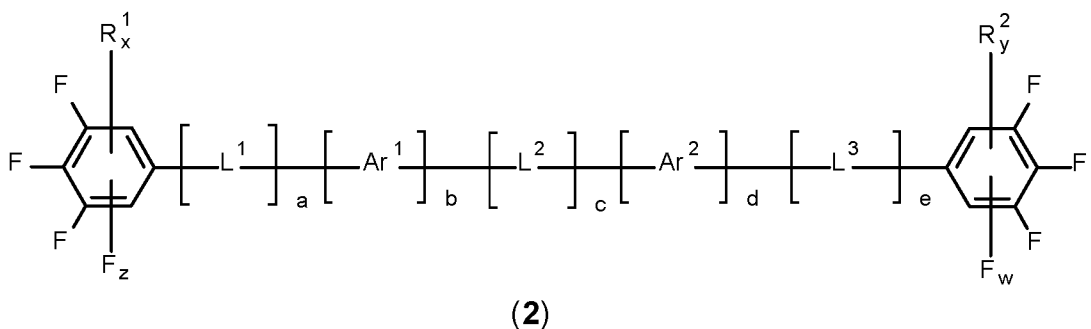
15 8. A process for the preparation of the compounds of formula



of claim 2,

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which process comprises the step of reacting a compound of formula



25 wherein a, b, c, d, e, x, y, z, w, Ar¹, Ar², L¹, L³, L², R¹ and R² are as depicted for the compound of formula (1),

with $M^{m+}(N_3^-)_m$,

wherein m is 1, 2 or 3, and M is a metal.

- 5 9. A solution comprising one or more compounds of formula (1) of any of claims 1 to 7, one or more polymers and one or more solvents.
10. The solution of claim 9, wherein the one or more polymers are dielectric polymers.
- 10 11. The solution of claim 10, wherein the one or more polymers are styrene-based polymers.
12. A process for the preparation of a device which process comprises the steps of (i) depositing the solution of any of claims 9 to 11 on a support in order to form a layer, and (ii) exposing the layer of step (i) to radiation in order to form a polymer layer.
- 15 13. The process of claim 12, wherein the device is an electronic device.
14. The process of any of claims 12 or 13, wherein the radiation of step (ii) has a wavelength in the range of 300 to 450 nm.
- 20 15. A device obtainable by any of the processes of claims 12 to 14.
16. Use of the compounds of formula (1) of any of claims 1 to 7 as cross-linker for crosslinking one or more polymers.

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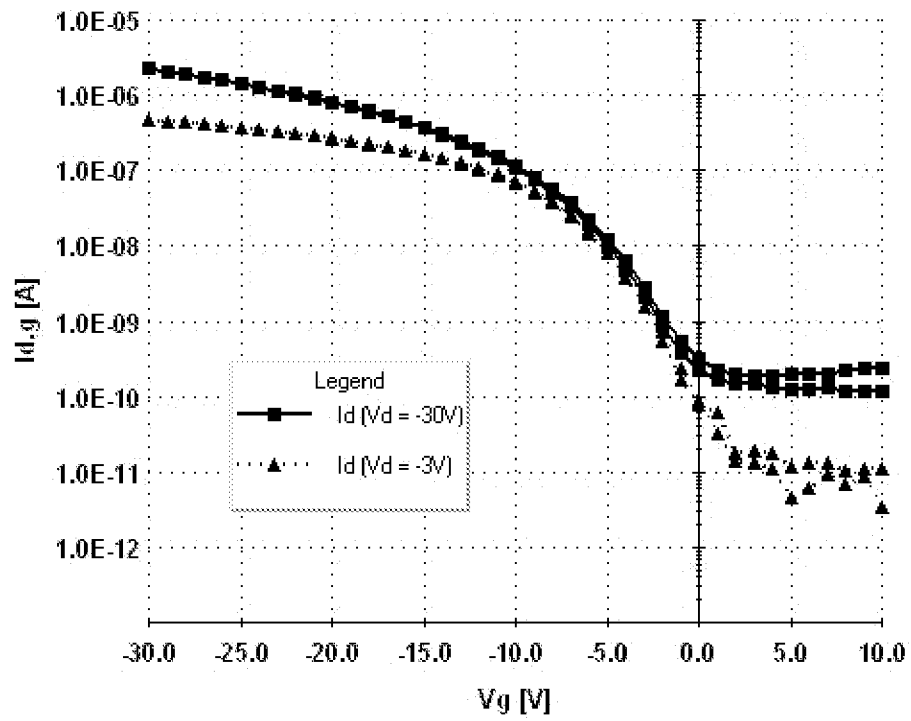


Figure 1

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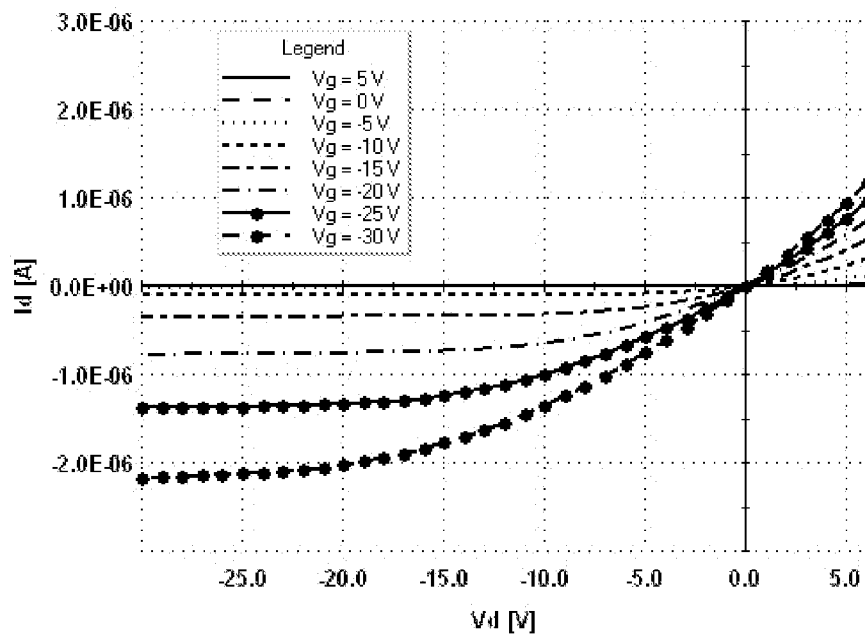
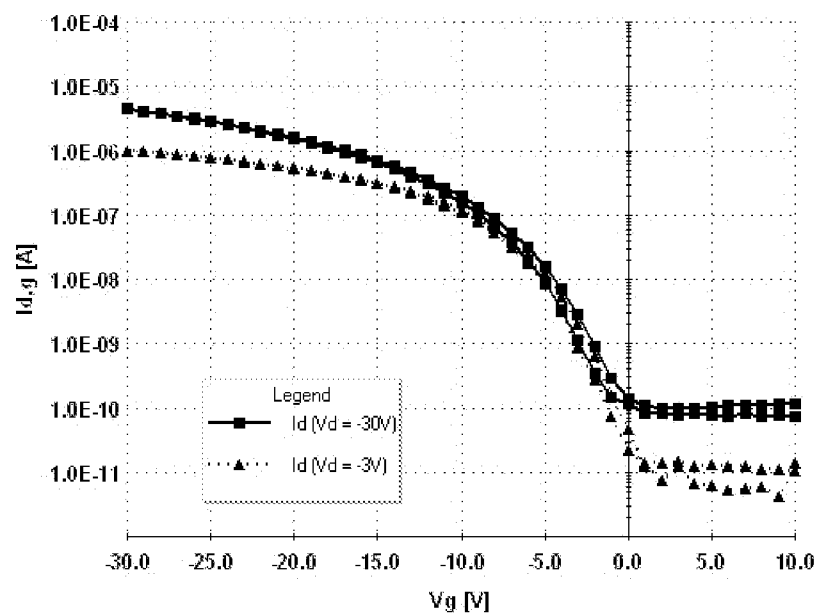


Figure 2

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5 Figure 3

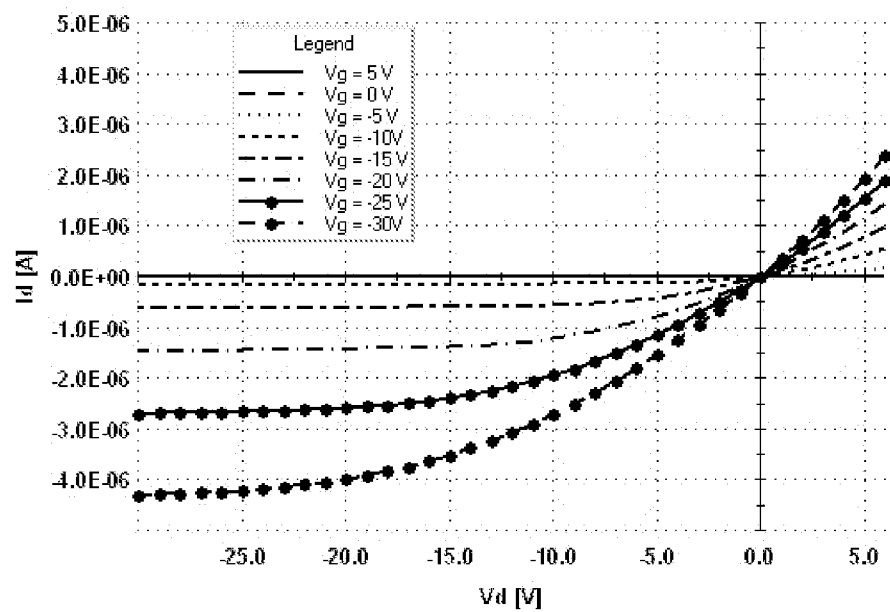
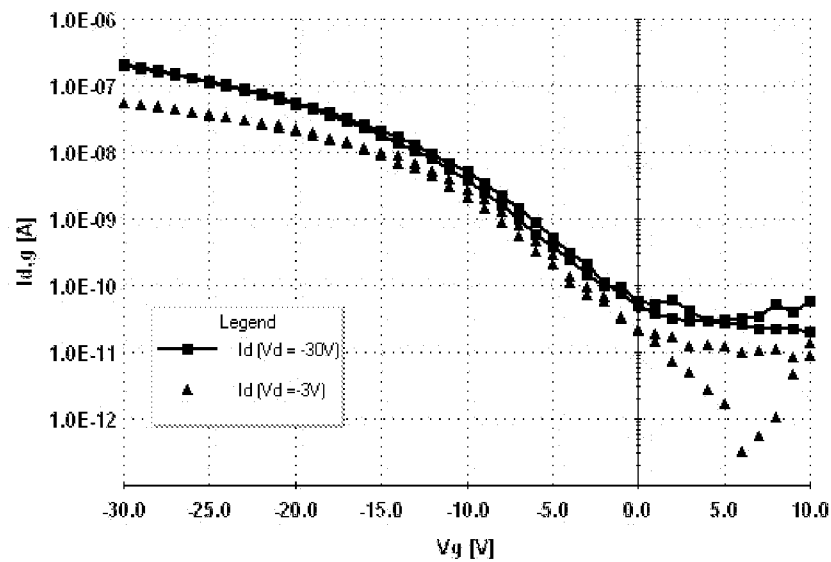
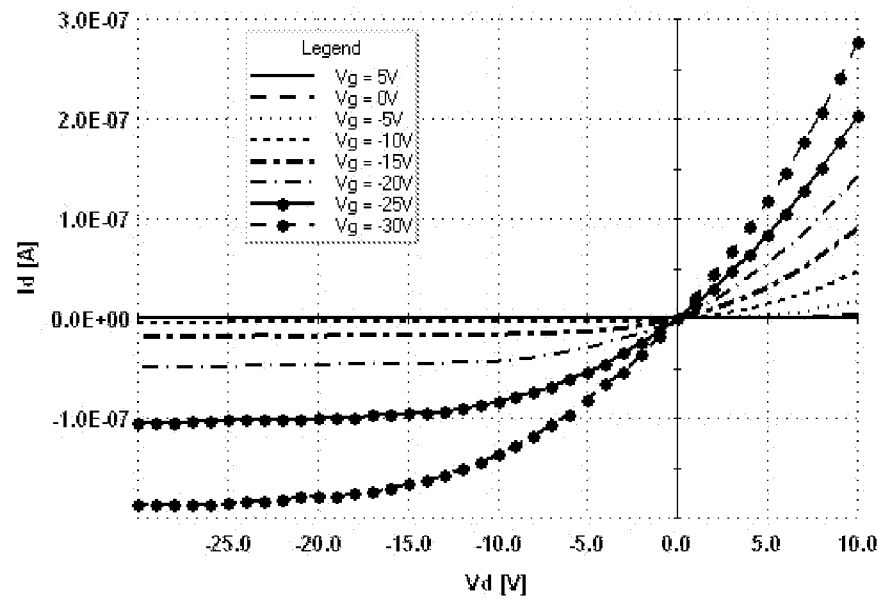


Figure 4



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Figure 5



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Figure 6

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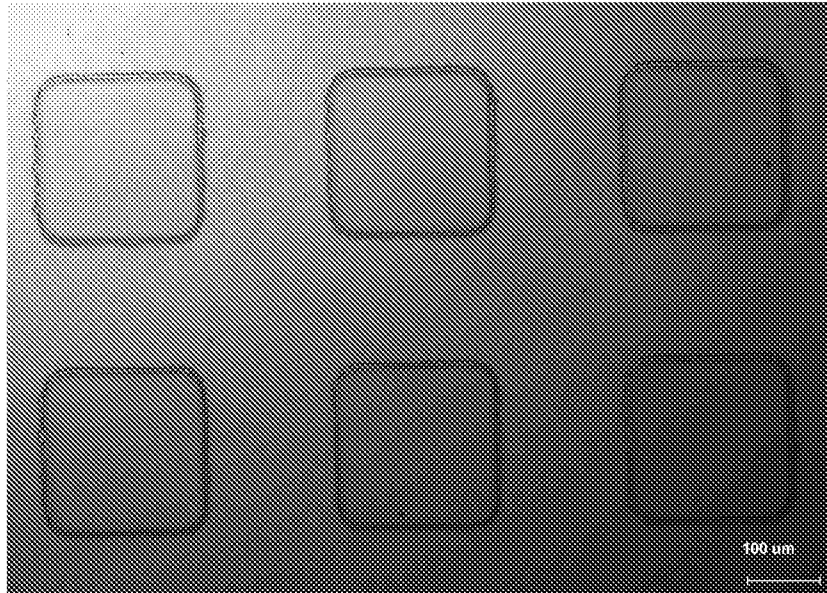
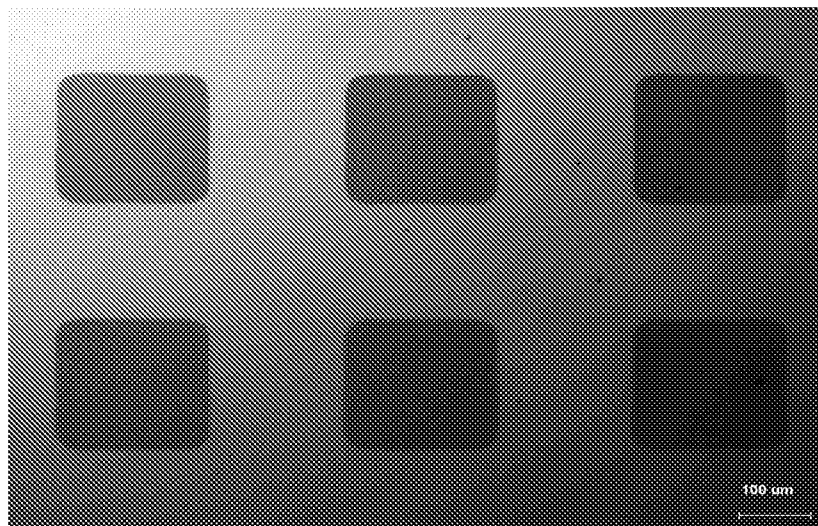


Figure 7

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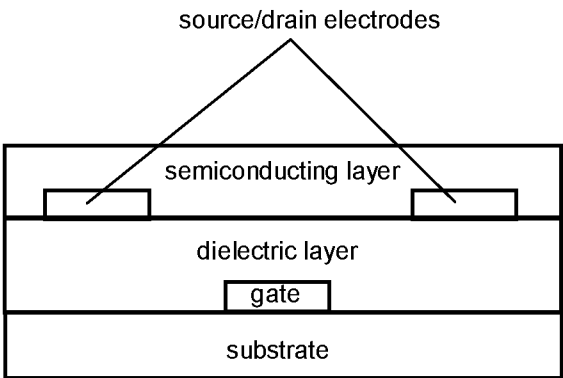
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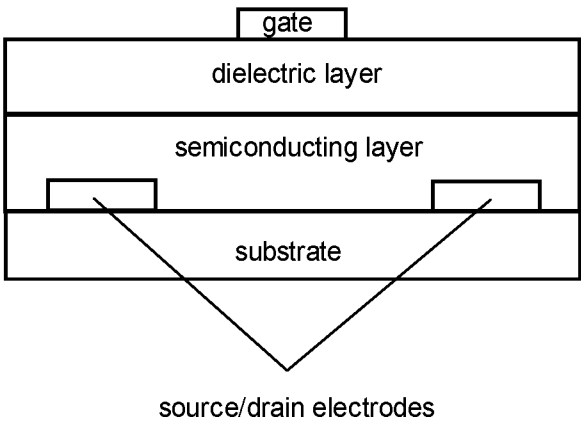
25 Figure 8

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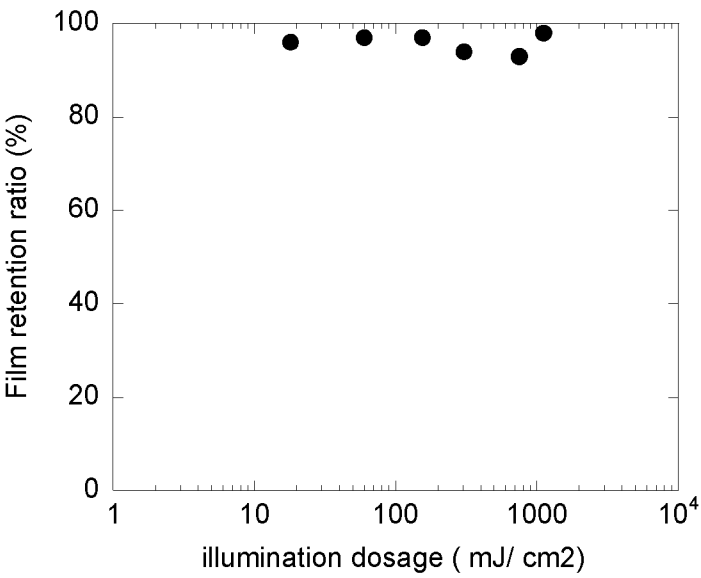


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Figure 9

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Figure 10



5 Figure 11

INTERNATIONAL SEARCH REPORT

International application No.

PCT/IB2014/062720

A. CLASSIFICATION OF SUBJECT MATTER

C08K 5/28(2006.01)i; C07C 247/00(2006.01)i; C07C 247/16(2006.01)i

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

C07C247/-; C08K5/-

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

CNKI,CPRS,CNABS,CNTXT,VEN,EPDOC,STN(Registry,CAPLUS):cross, crosslink+, azide, crosslink?, linker?, LED, FET,polymer, barrier layer,patterning, electro?, device?,bisazide

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	WO 2011068482 A1 (NATIONAL UNIV.OF SINGAPORE) 09 June 2011 (2011-06-09) Claims 1-23, examples 1-10	1-16
A	WO 2004100282 A2 (CAMBRIDGE UNIV. TECHNICAL SERVICES LIMITED.) 18 November 2004 (2004-11-18) the whole of description	1-16
A	WO 2005052027 A1 (DOW GLOBAL TECHNOLOGIES INC.) 09 June 2005 (2005-06-09) the whole of description	1-16

☐ Further documents are listed in the continuation of Box C.☒ See patent family annex.

* Special categories of cited documents:

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“E” earlier application or patent but published on or after the international filing date

“L” document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)

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“P” document published prior to the international filing date but later than the priority date claimed

“T” later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

“X” document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

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“&” document member of the same patent family

Date of the actual completion of the international search

14 November 2014

Date of mailing of the international search report

25 November 2014

Name and mailing address of the ISA/CN

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INTERNATIONAL SEARCH REPORT
Information on patent family members

International application No.

PCT/IB2014/062720

Patent document cited in search report			Publication date (day/month/year)	Patent family member(s)			Publication date (day/month/year)
WO	2011068482	A1	09 June 2011	US	2012244294	A1	27 September 2012
				JP	2013512986	A	18 April 2013
				EP	2507309	A1	10 October 2012
				EP	2507309	A4	03 July 2013
WO	2004100282	A2	18 November 2004	JP	4500304	B2	14 July 2010
				DE	602004015103	D1	28 August 2008
				JP	2007527542	A	27 September 2007
				EP	1631995	A2	08 March 2006
				KR	101172526	B1	13 August 2012
				US	8530269	B2	10 September 2013
				KR	20060030025	A	07 April 2006
				AT	401672	T	15 August 2008
				WO	2004100282	A3	20 January 2005
				EP	1631995	B1	16 July 2008
				US	2007172978	A1	26 July 2007
WO	2005052027	A1	09 June 2005	KR	20060100415	A	20 September 2006
				GB	0611893	D0	26 July 2006
				JP	2011251984	A	15 December 2011
				KR	101196513	B1	01 November 2012
				JP	5209207	B2	12 June 2013
				DE	112004002204	T5	26 October 2006
				US	2007096082	A1	03 May 2007
				KR	20120101163	A	12 September 2012
				JP	2007511636	A	10 May 2007
				CN	102796260	A	28 November 2012
				KR	20110121729	A	08 November 2011
				JP	5209763	B2	12 June 2013
				TW	201219350	A	16 May 2012
				CN	1886443	B	01 May 2013
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				US	2013085258	A1	04 April 2013
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